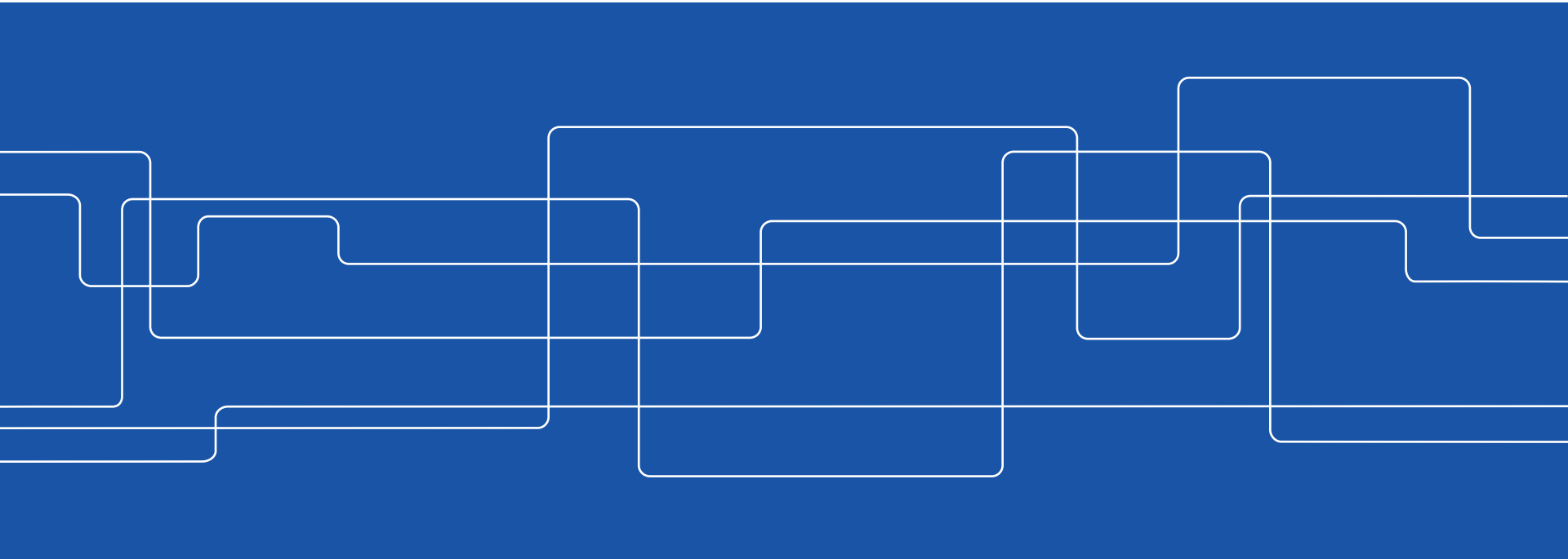




# Unconventional Micro-Manufacturing and Integration Technologies

Frank Niklaus





# Outline

- Background
- Micro-Manufacturing and Integration Research
  - Heterogeneous 3D Integration for MEMS & NEMS
  - Integration and Packaging for MEMS
  - Nanofabrication Technologies and Graphene NEMS
- Summary



# KTH Royal Institute of Technology

Sweden's largest technical university:

- More than 13,000 full-time students.
- Close to 1,800 research students.
- Around 3,500 full-time positions.



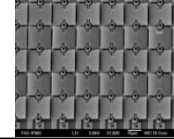
# Department of Micro- and Nanosystems



**Head: Prof. Göran Stemme**

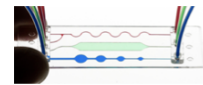
- Micro and Nanosystem Integration

Prof. Frank Niklaus



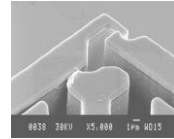
- Lab-on-a-Chip and Polymer Devices

Prof. Wouter van der Wijngaart



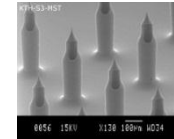
- Microwave and THz MEMS

Prof. Joachim Oberhammer



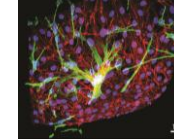
- Biomedical Devices

Assoc. Prof. Niclas Roxhed



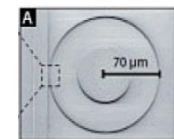
- Bioelectric Hybrid Systems

Ass. Prof. Anna Herland



- Photonic MEMS

Ass. Prof. Kristinn Gylfason





# Thanks to all Colleagues at KTH !

## Support

- Erika Appel Admin. Ass.
- Ulrika Pettersson Admin. Ass.
- Mikael Bergqvist Technician
- Cecilia Aronsson Technician

## Researchers

- Göran Stemme Prof.
- Wouter van der Wijngaart Prof.
- Joachim Oberhammer Prof.
- Niclas Roxhed Assoc. Prof.
- Kristinn B. Gylfason Assis. Prof.
- Anna Herland Assis.Prof.
- Hans Sohlström Assoc. Prof.
- Tommy Haraldsson Researcher
- Ilya Anoshkin Researcher
- Oleksandr Glubokov Researcher
- Jonas Hansson Researcher
- Petr Makhlov Researcher
- Umer Shah Researcher
- Simon Bleiker Researcher



## PhD Students

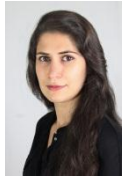
- Gabriel Lenk
- Floria Ottonello Briano
- Simone Pagliano
- Arne Quellmalz
- Mina Rajabi
- Federico Ribet
- Stephan Schröder
- Serguei Smirnov
- Fritzi Töpfer
- Alexander Vastesson
- Xiaojing Wang
- Reza Zandi Shafagh
- Zhou Xiamo
- Zhao Xinghai
- James Campion
- Valentin Dubois
- Alessandro Enrico
- Xuge Fan
- Jessica Liljeholm
- Linnea Gustafsson
- Maoxiang Guo
- Weijin Guo
- Carlos Errando Herranz
- Emre Iseri
- Staffan Johansson
- Aleksandr Krivovitca
- Laila Ladhani
- Miku Laakso
- Torben Last





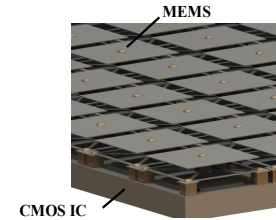
# Micro and Nanosystem Integration Group

- 8 Ph.D. students at MST
- 2 industrial Ph.D. students at SenseAir and Silex Microsystems
- 1 postdoc and 3 contributing senior researchers

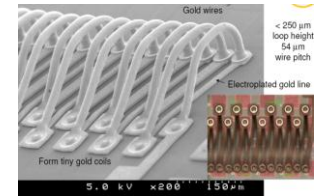


# Four Research Topics

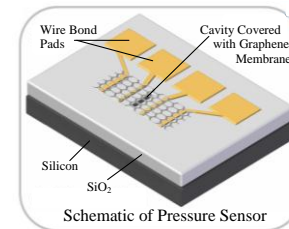
- Heterogeneous 3D Integration Technologies for MEMS and NEMS



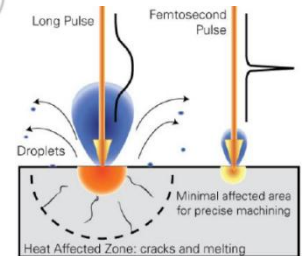
- Integration and Packaging for MEMS



- Nanofabrication Technologies and Graphene-Based NEMS



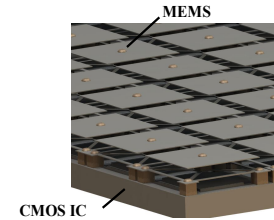
- Femtosecond Laser-Based Micromachining for MEMS & NEMS





# *Research Topics in Group*

- **Heterogeneous 3D Integration for MEMS & NEMS**



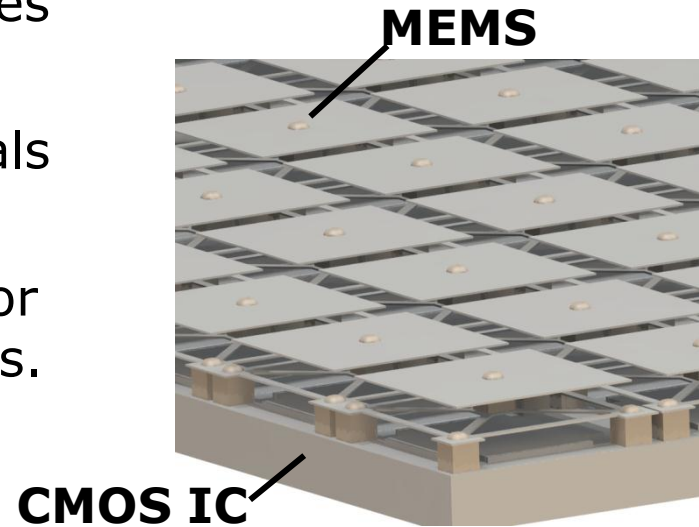
- Integration and Packaging for MEMS
- Nanomanufacturing Technologies and Graphene NEMS



# Heterogeneous 3D Integration for MEMS & NEMS

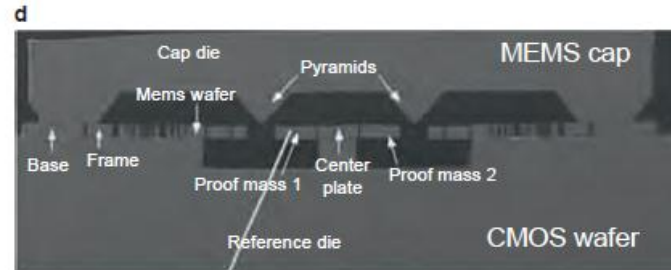
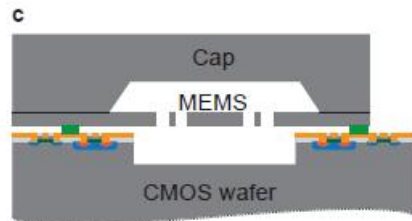
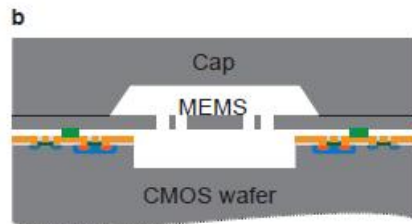
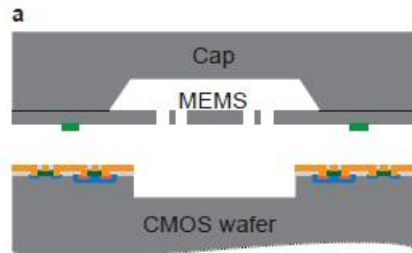
## Motivation

- New MEMS designs, functionalities and material combinations.
- High performance MEMS materials on standard foundry ICs.
- Very high integration densities for smaller and cheaper components.

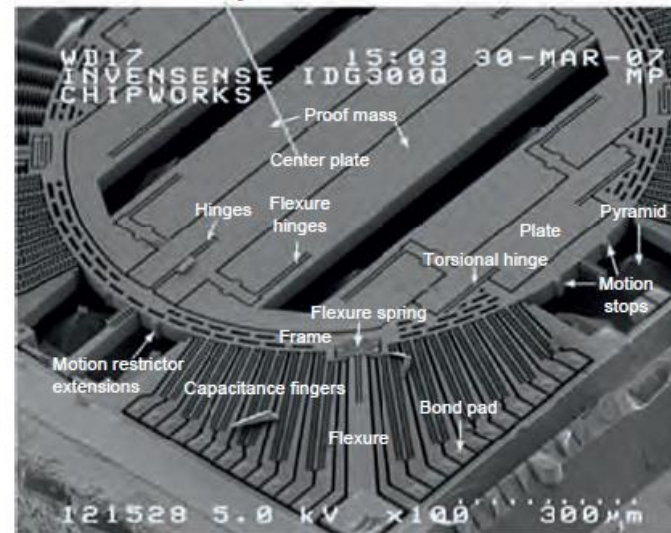


# 3D Integrated MEMS on ICs

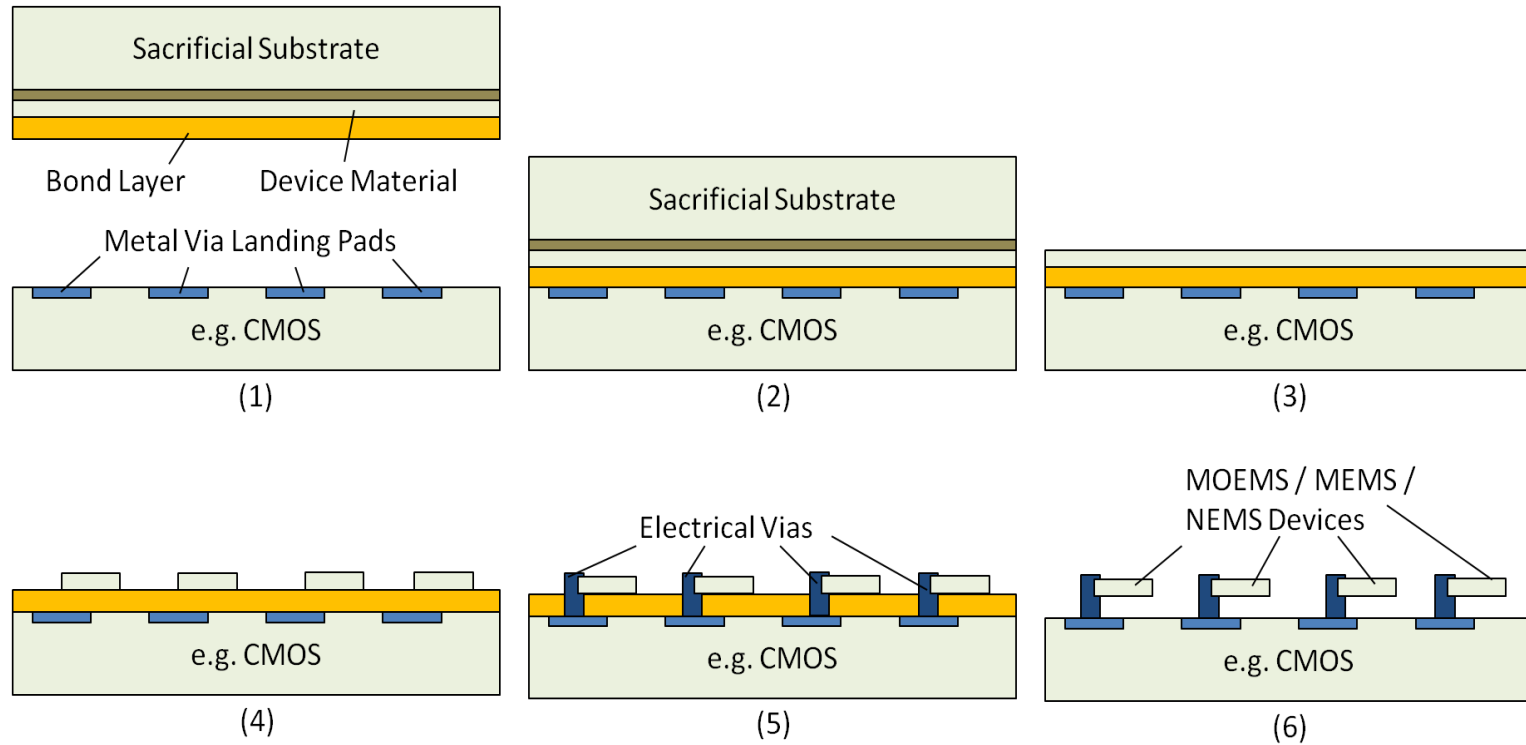
## Commercial Examples: Invensense (gyro), mCube (accel.)



MEMS Gyro



# Via-Last Heterogeneous 3D Integration Platform

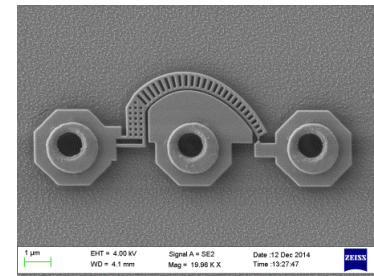
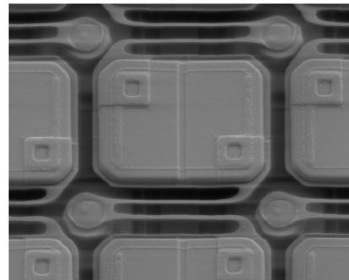
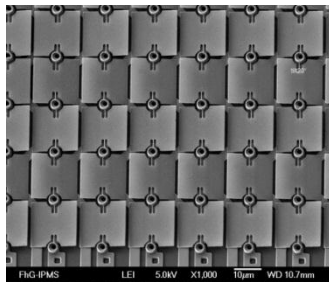


## Advantages

- No wafer-to-wafer alignment.
- Extreme reduction of via and dimensions (sub  $\mu\text{m}$ ) possible.

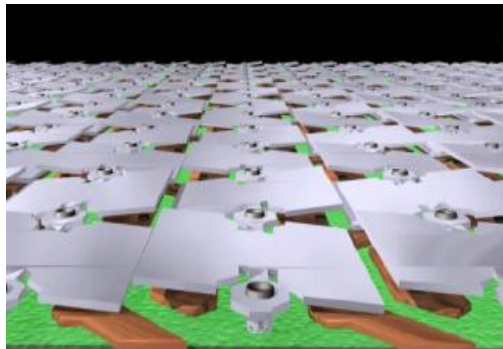
# Implemented Applications

- Si Micromirror Arrays
- IR Bolometer Arrays
- NEM Relays

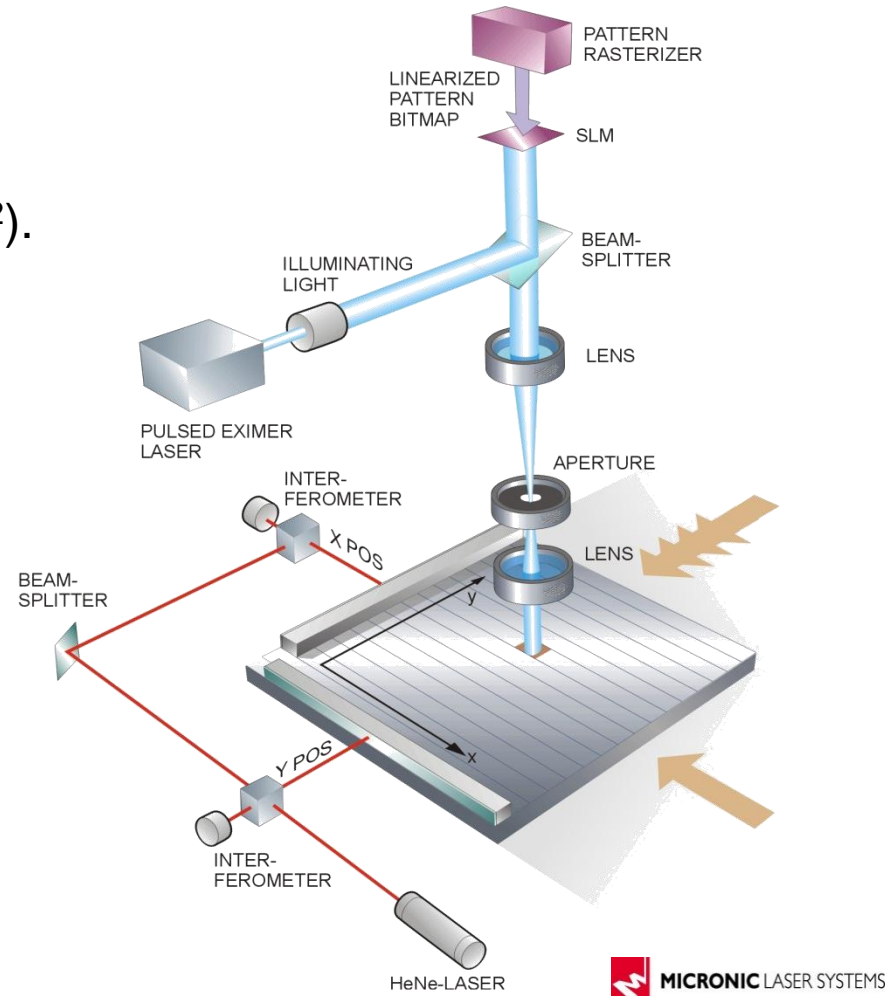


# Tilting Micro-Mirror Arrays (SLMs) for Maskless DUV Lithography Systems

- Step and repeat maskless lithography.
- 1 million mirrors (mirror size  $16 \times 16 \mu\text{m}^2$ ).
- Single mirror actuation with underlying CMOS.
- Analogue tilt actuation in 16 steps (gray-tones) possible.

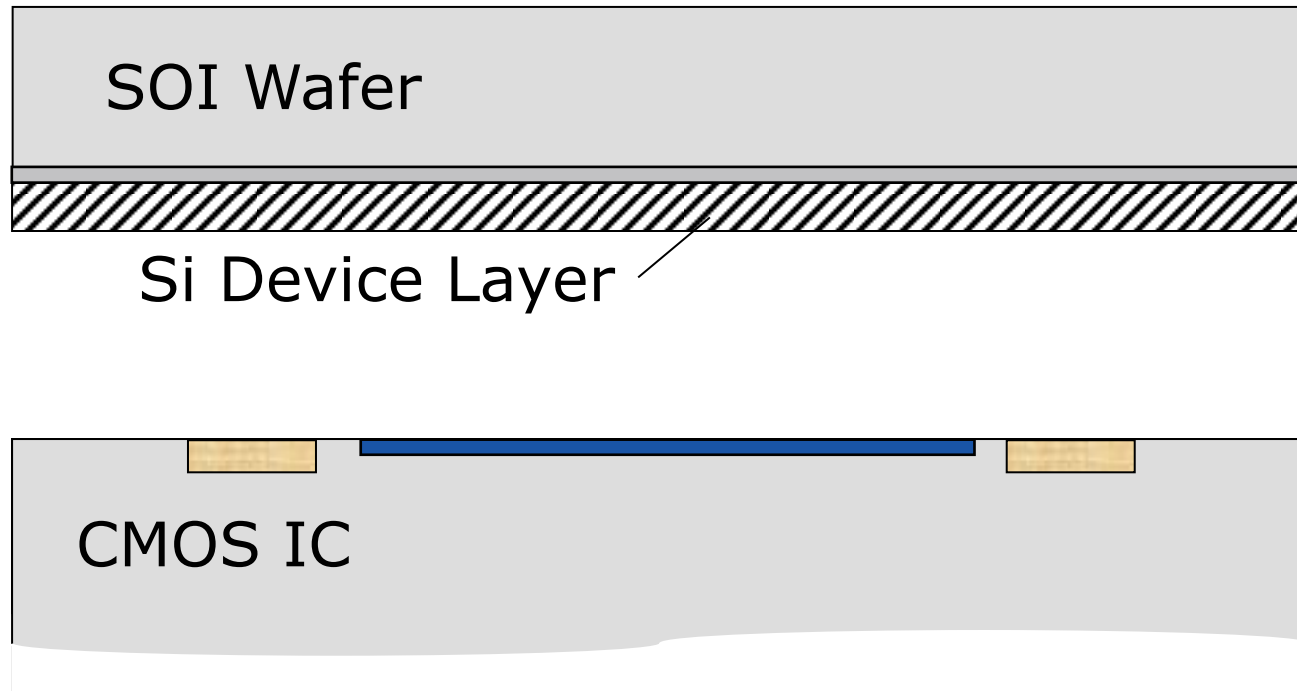


Source: Zimmer, Fraunhofer IPMS



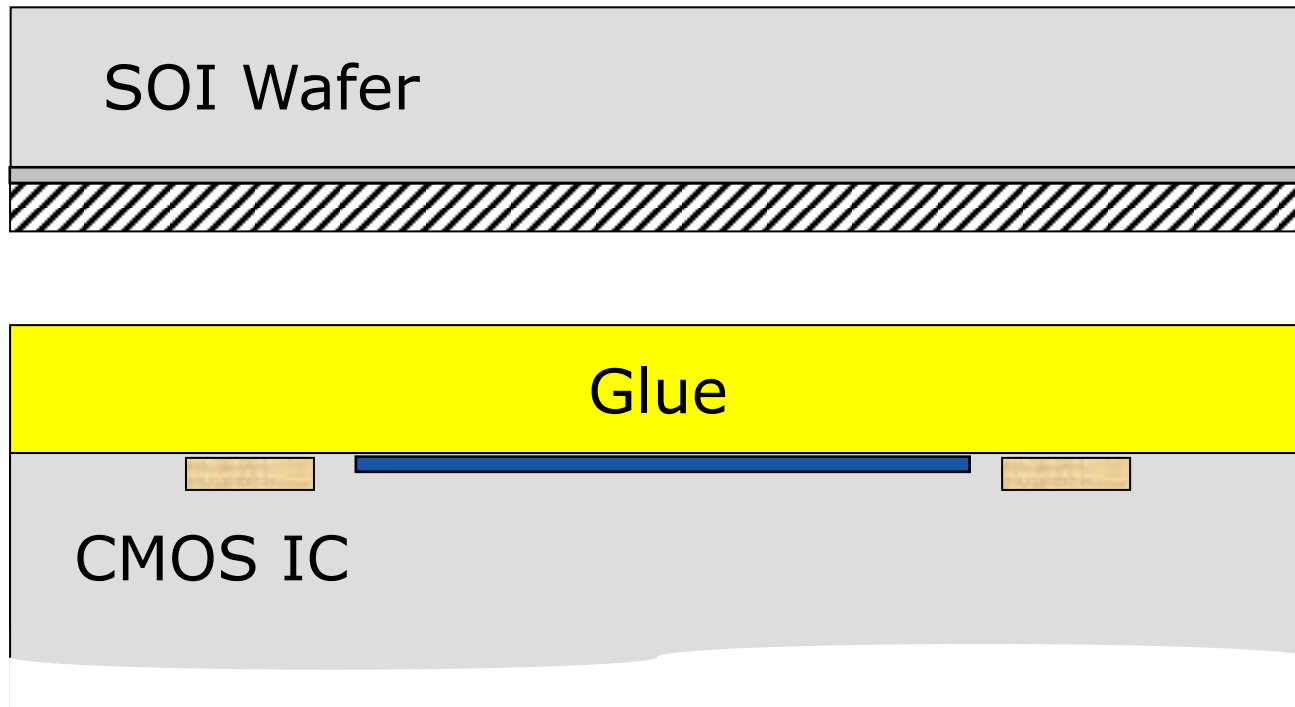


# Via-Last Heterogeneous Integration for Mono-Crystalline Si Mirrors on CMOS

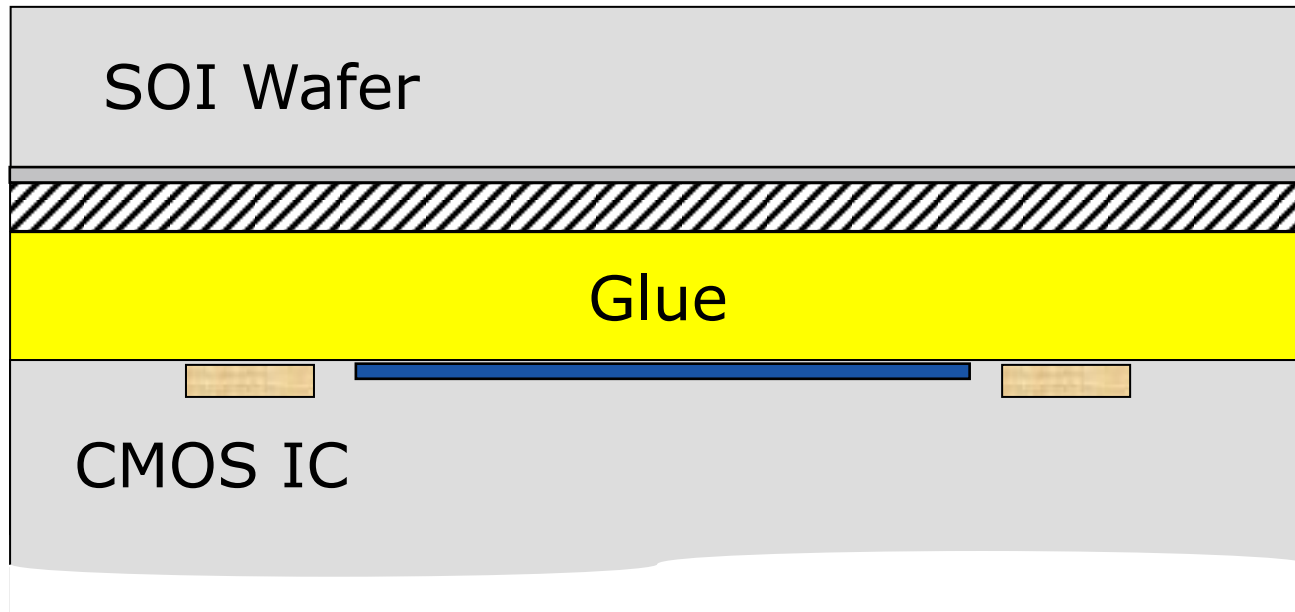




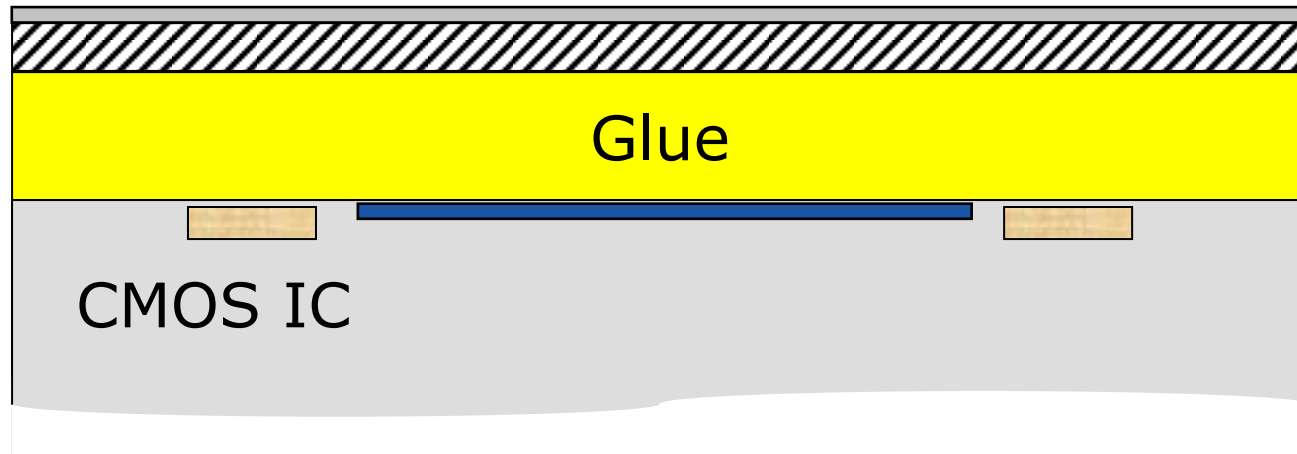
# Si Mirror Integration: Dispense Glue



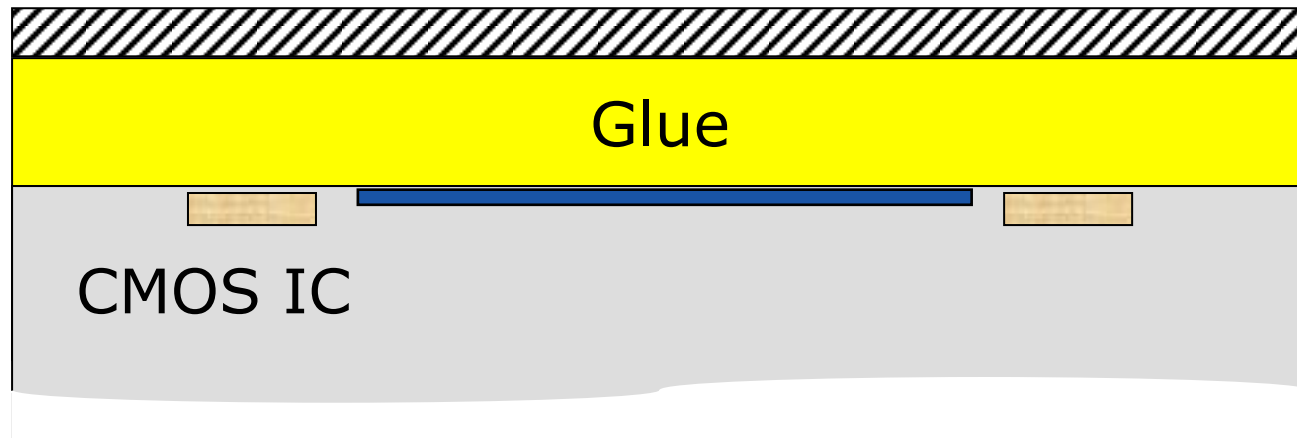
# Si Mirror Integration: Adhesive Wafer Bonding



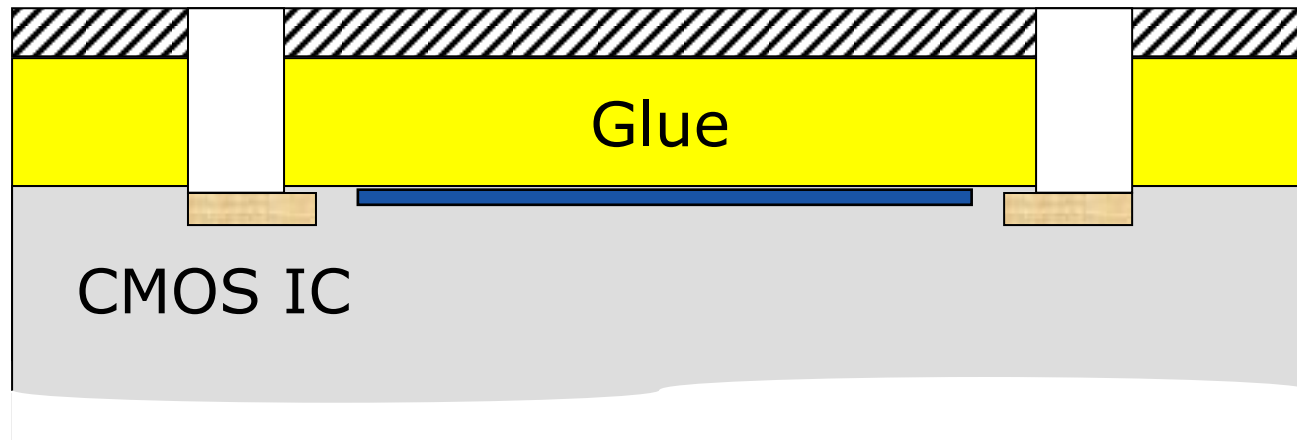
# Si Mirror Integration: Sacrificial Wafer Thinning



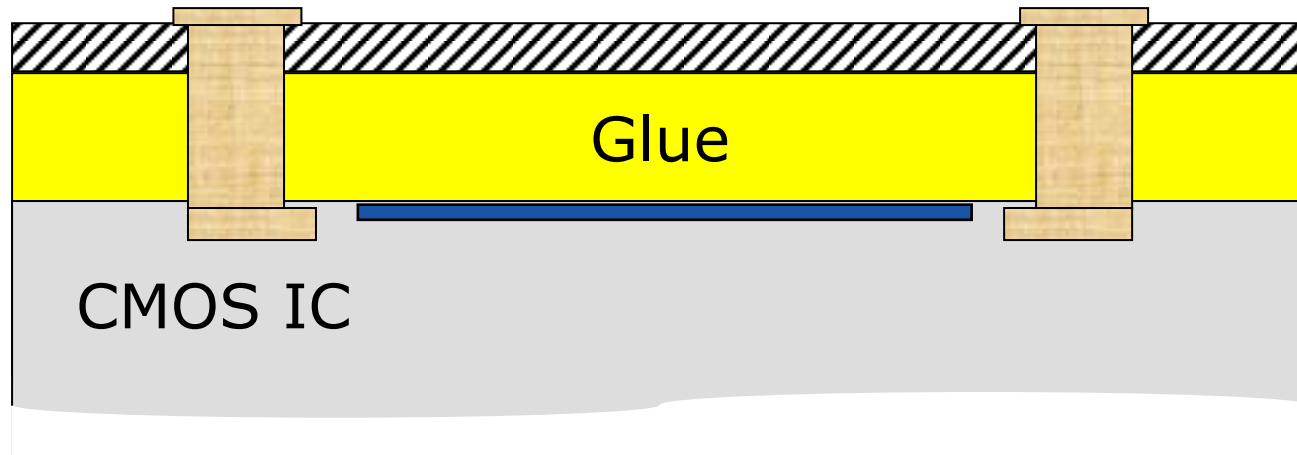
# Si Mirror Integration: Removal of $\text{SiO}_2$ Etch-Stop



# Si Mirror Integration: Via Etch

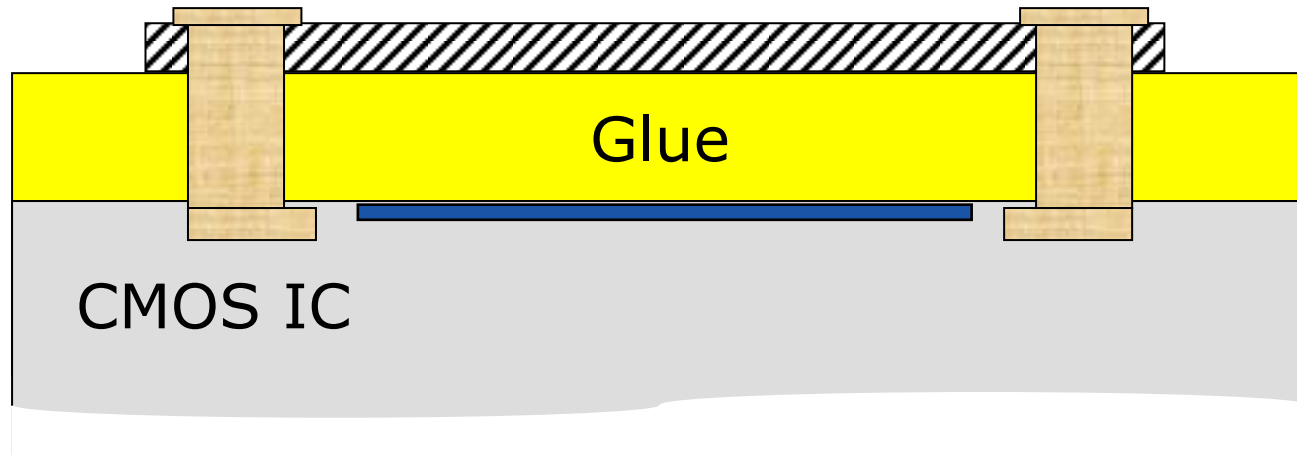


# Si Mirror Integration: Via Formation

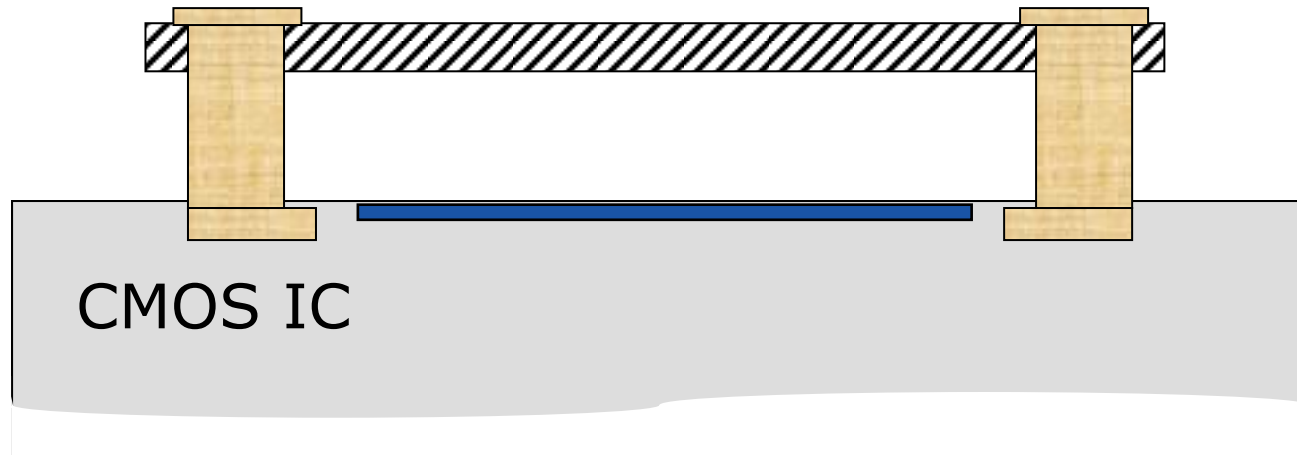




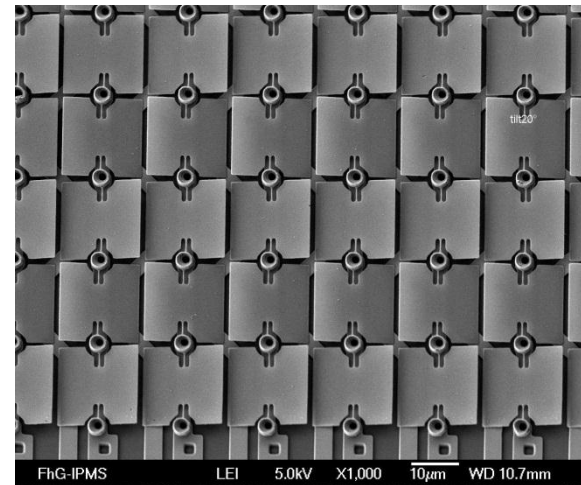
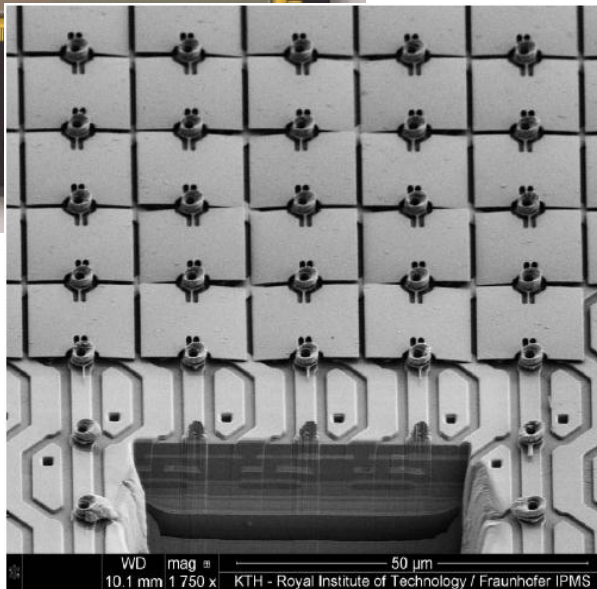
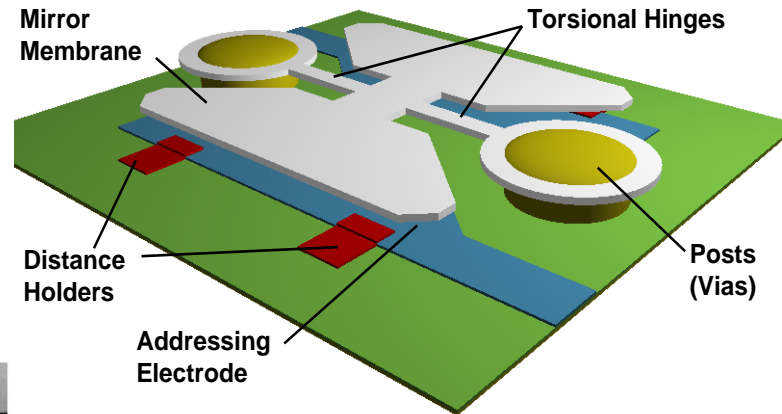
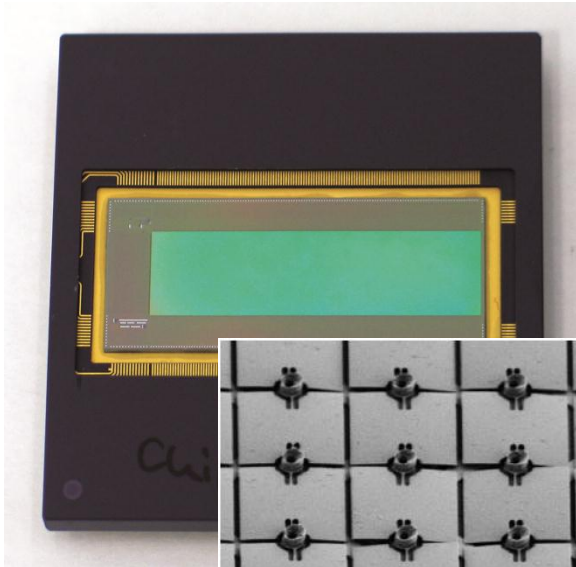
# Si Mirror Integration: Mirror Formation



# Si Mirror Integration: Mirror Release

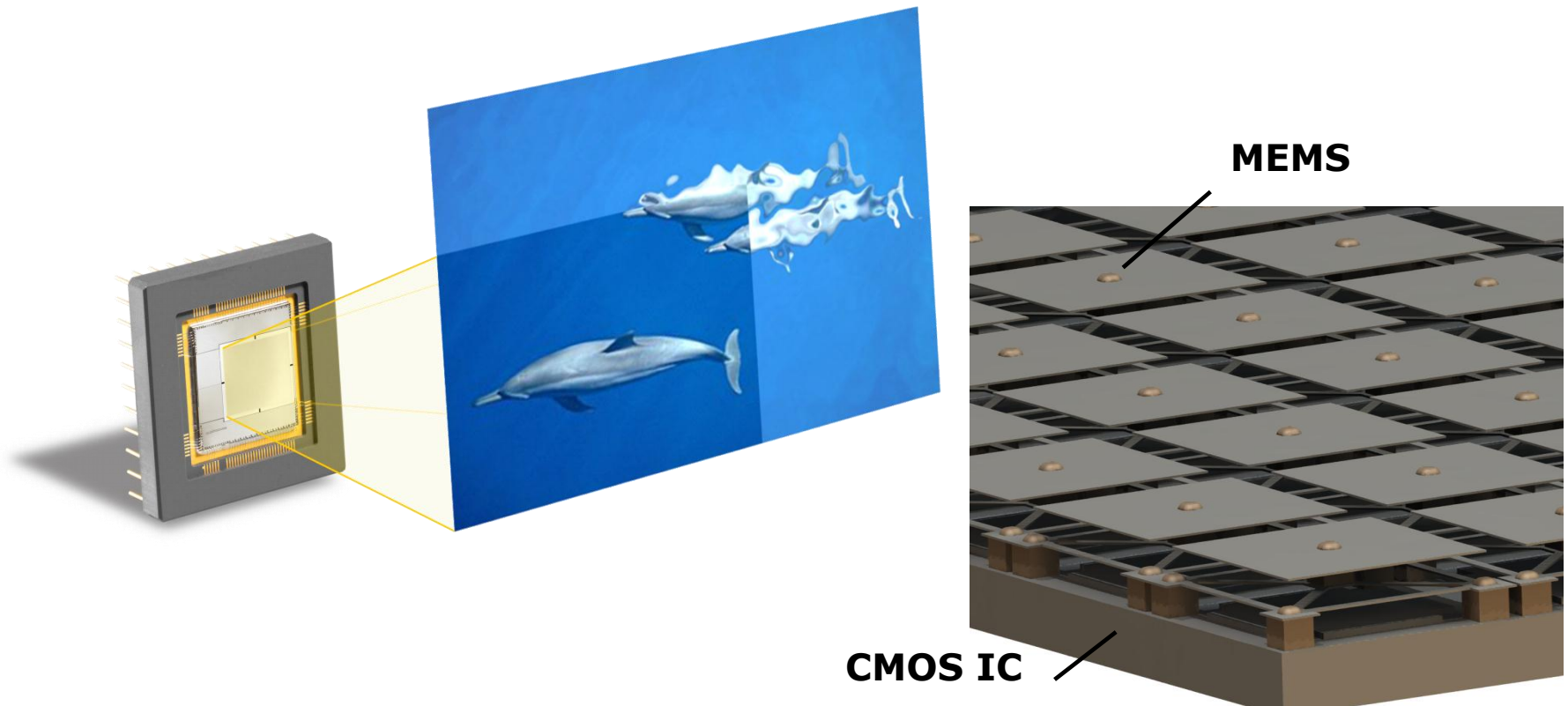


# 1 M-pixel Mono-Si Mirror Array on CMOS



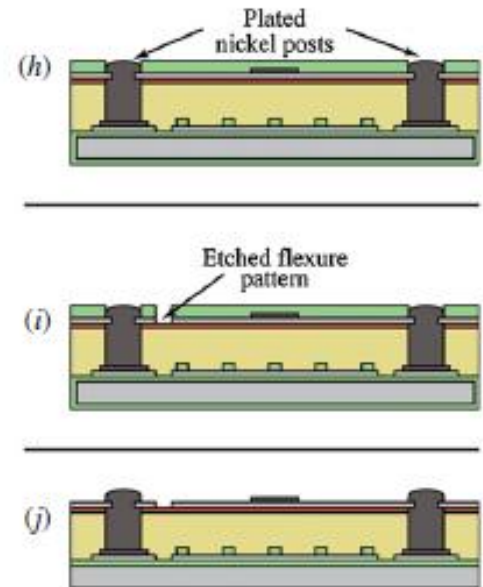
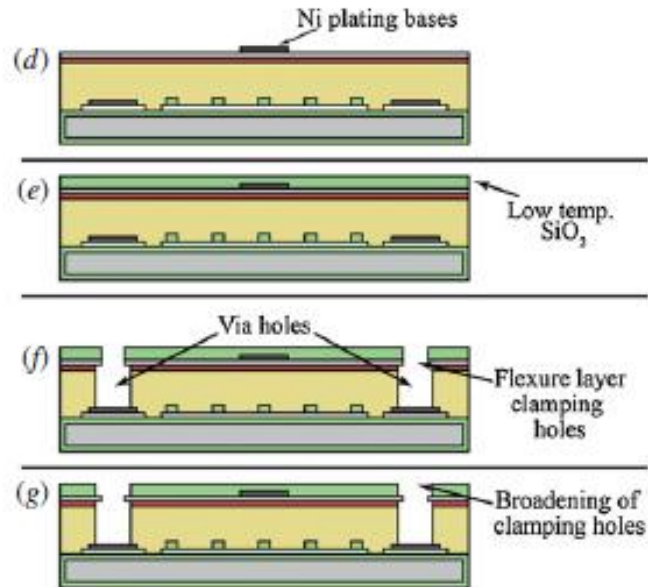
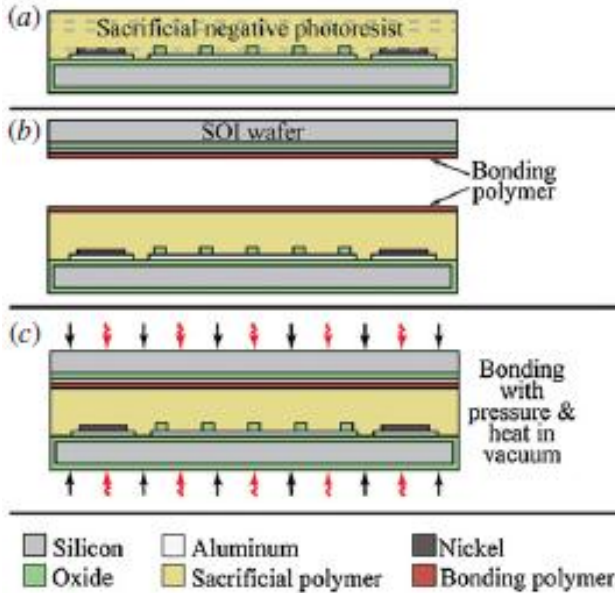
# SLMs for Adaptive Optics in Astronomy and Microscopy

## Wave-front correction using piston-type mirror arrays



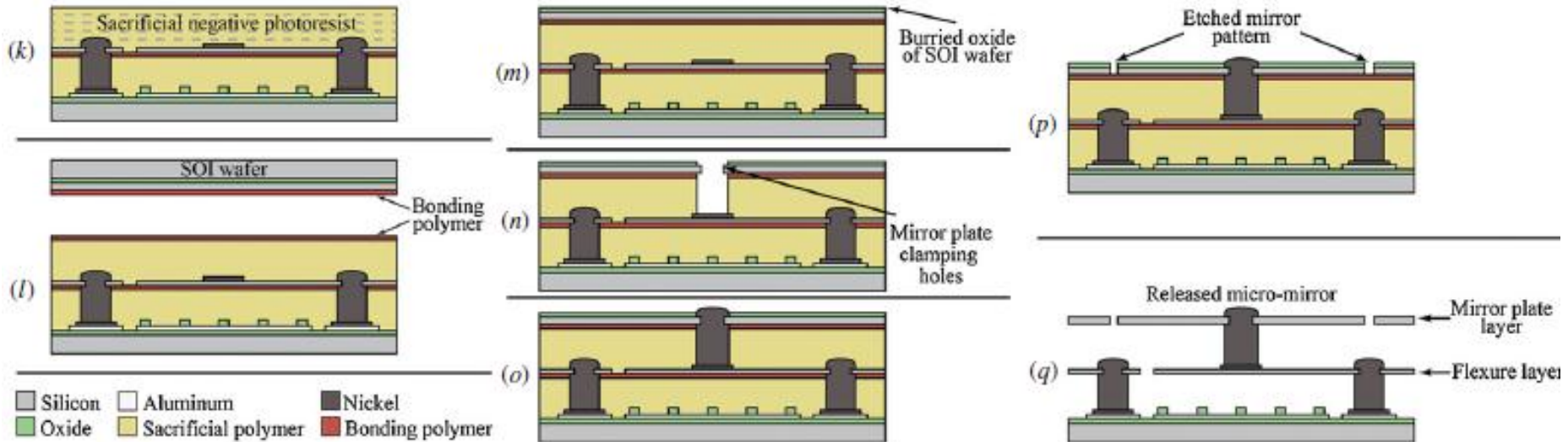
# 2-Layer SLMs Fabrication Process

## 1<sup>st</sup> heterogenous 3D integration sequence



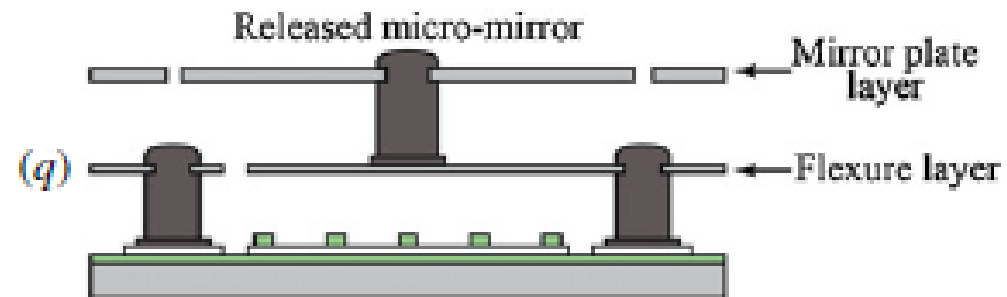
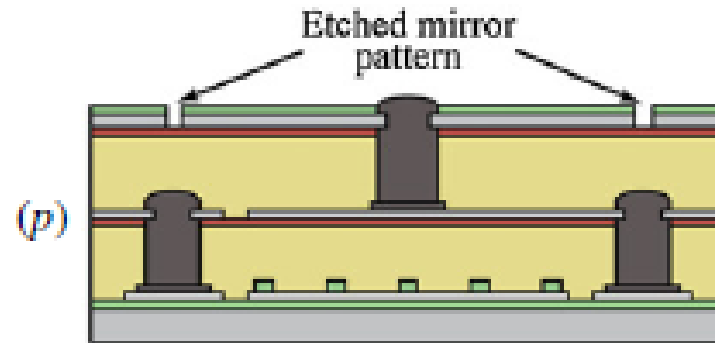
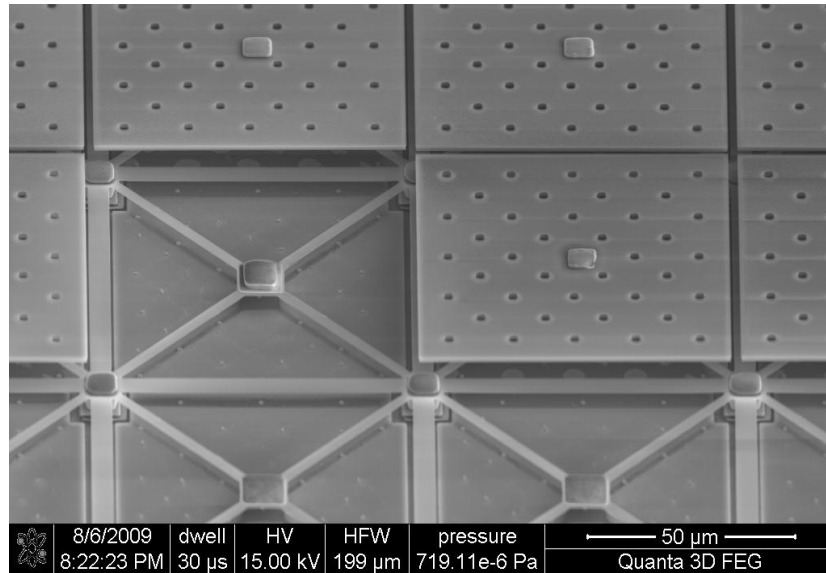
# 2-Layer SLMs Fabrication Process

2<sup>nd</sup> heterogenous 3D integration sequence

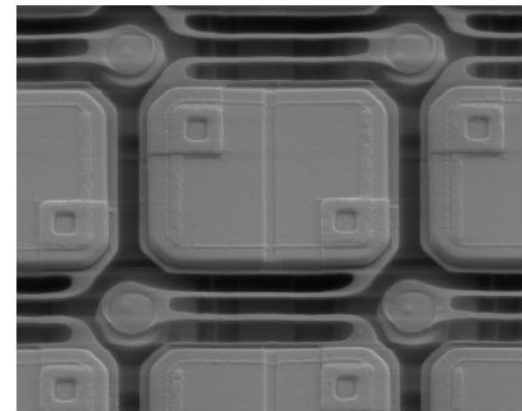
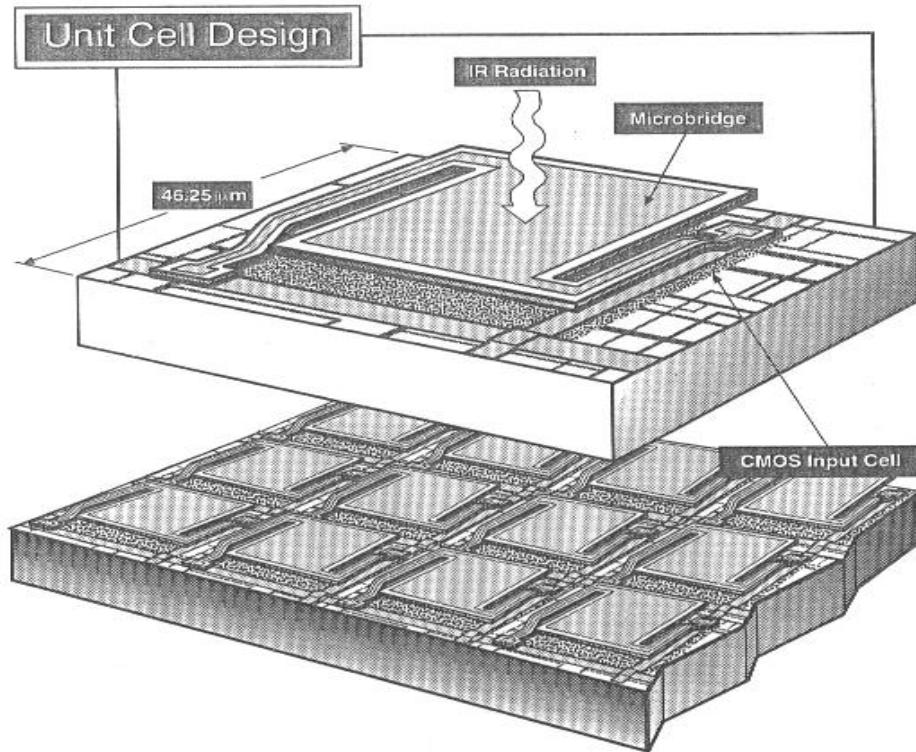




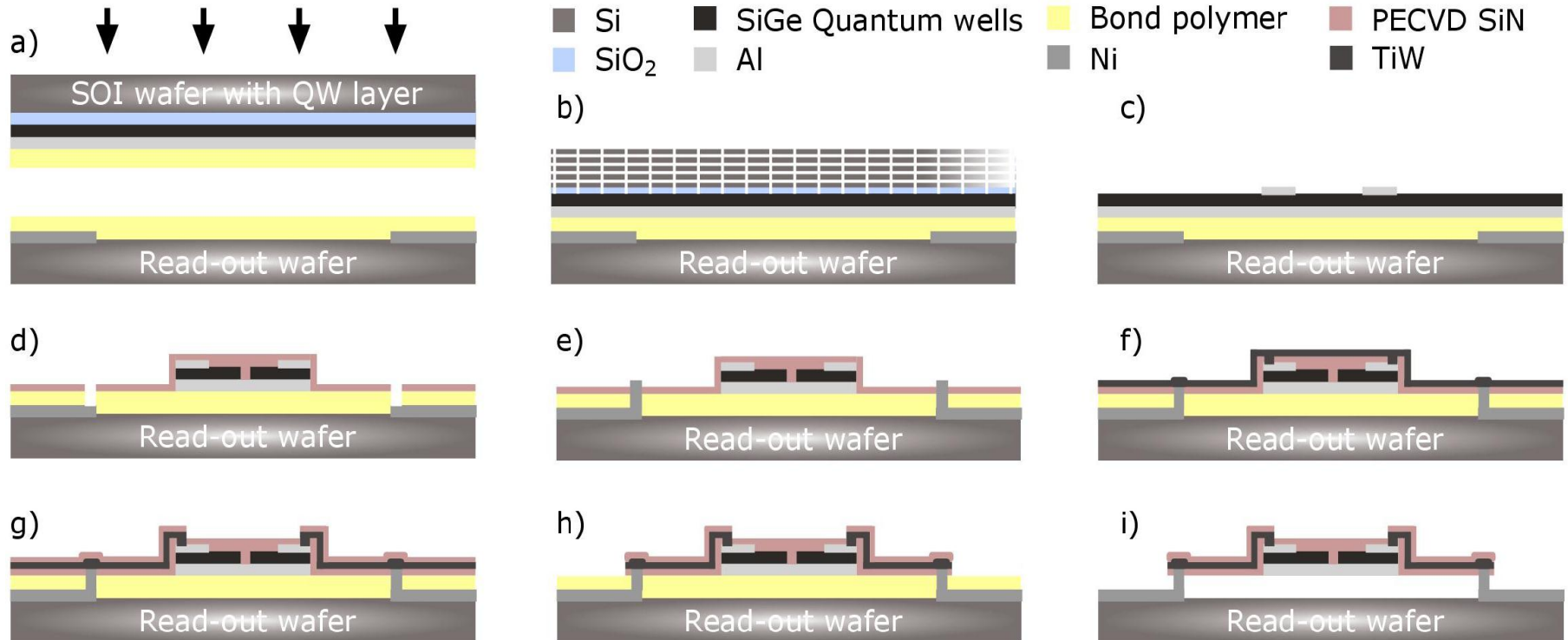
# Via-Last Heterogeneous Integration for Piston-Mirrors Using Two-Step Layer Transfer



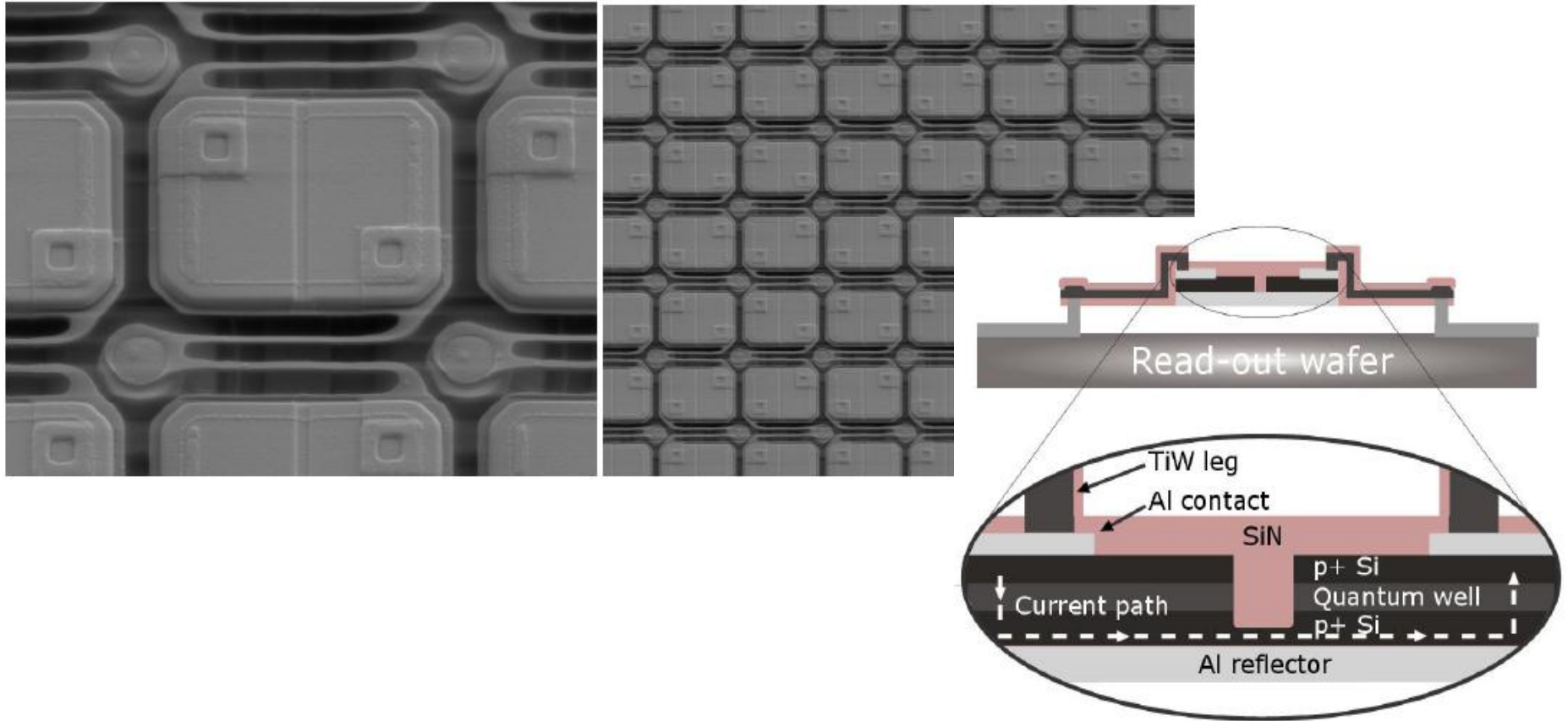
# Bolometer Array for IR Imaging



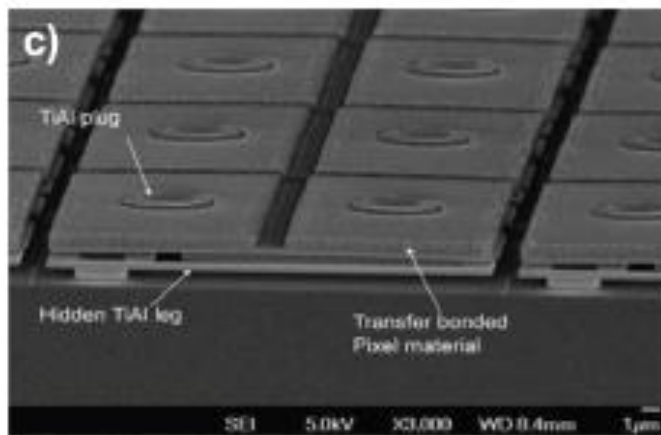
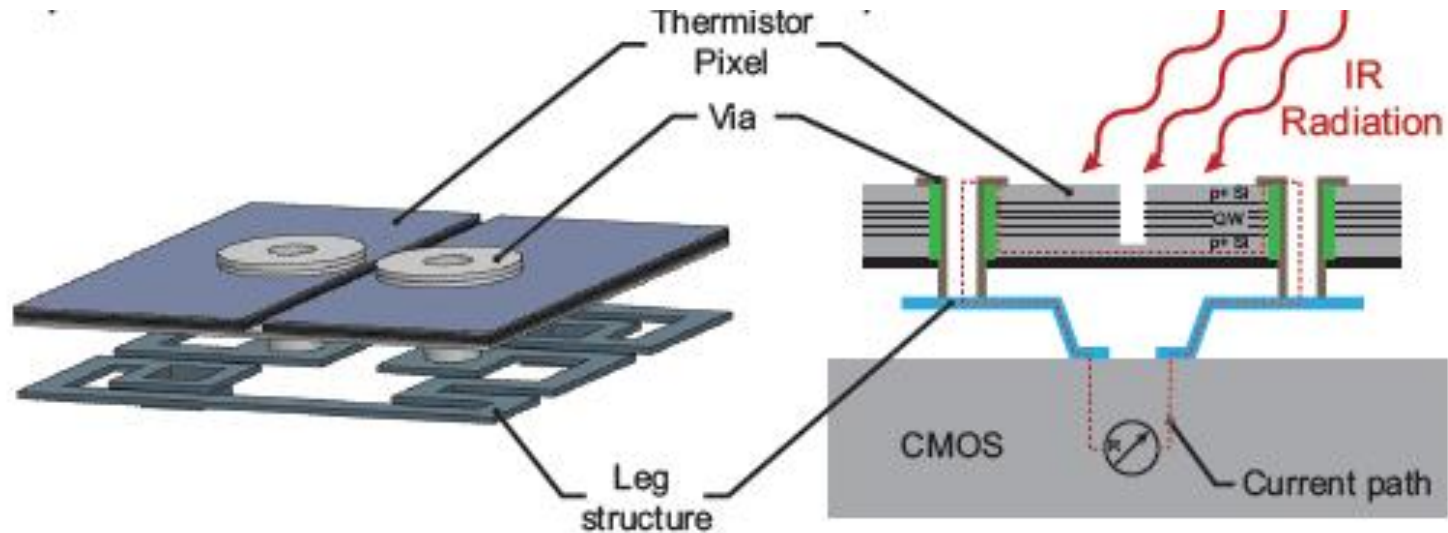
# Design of QW Si/SiGe IR Bolometer



# Heterogeneously Integrated 17 $\mu\text{m}$ pitch QW SiGe Bolometers on Fan-Out-Wafers

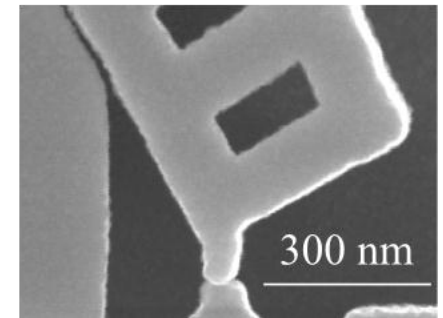
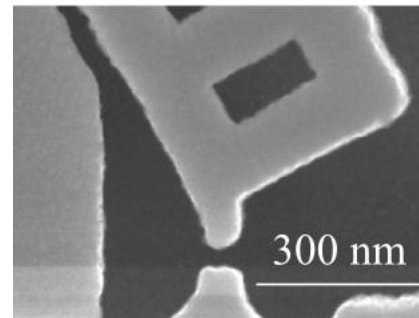
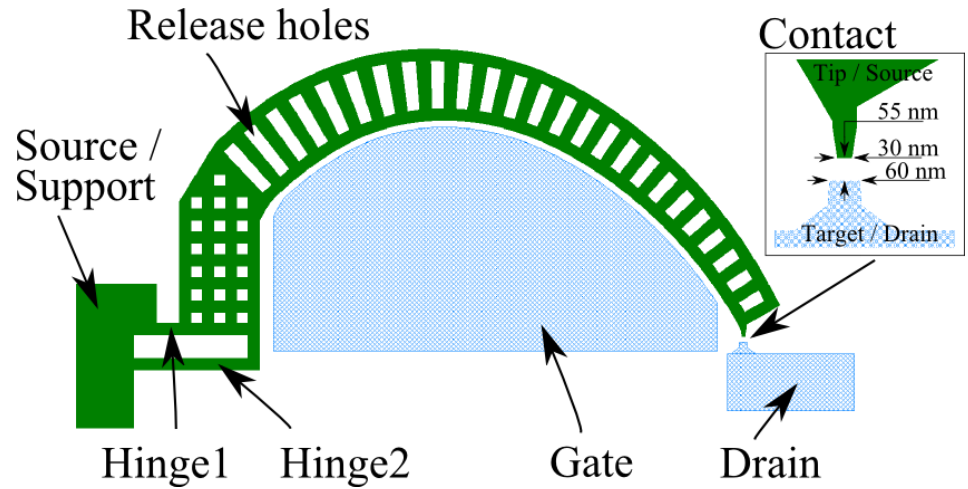
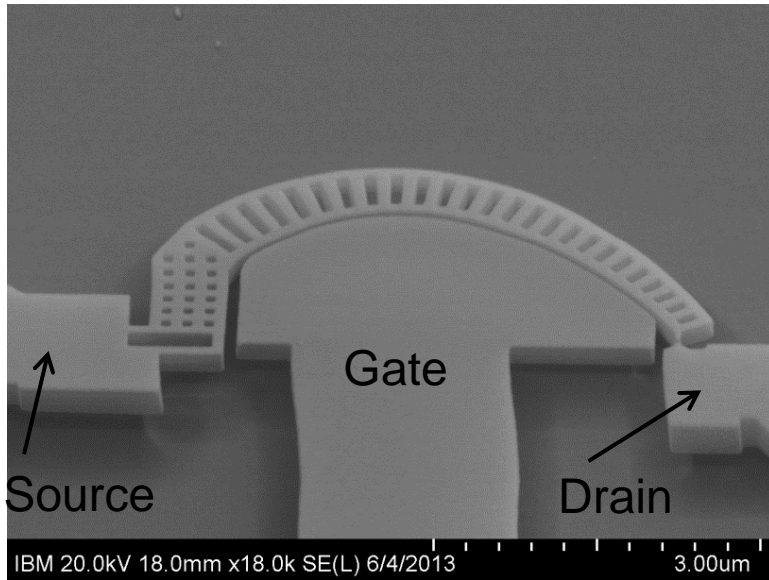


# Functional Double-Layer 25 $\mu\text{m}$ pitch IR Bolometers on 0.35 $\mu\text{m}$ CMOS





# NEMS Switch Design



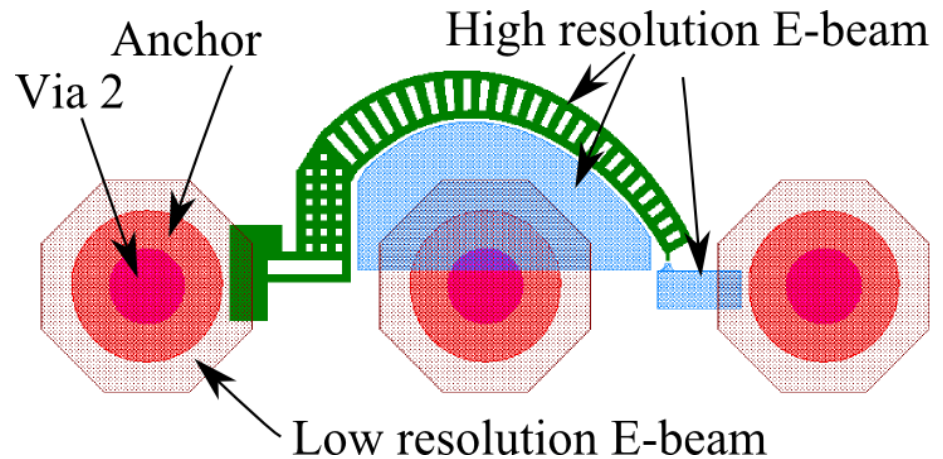
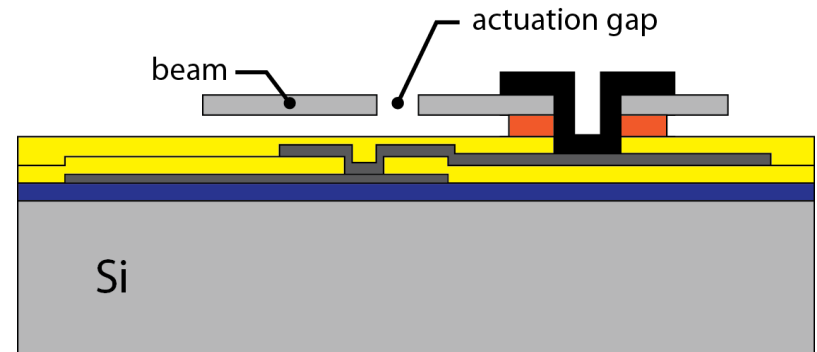
# Integration of NEM Switches

## Goal:

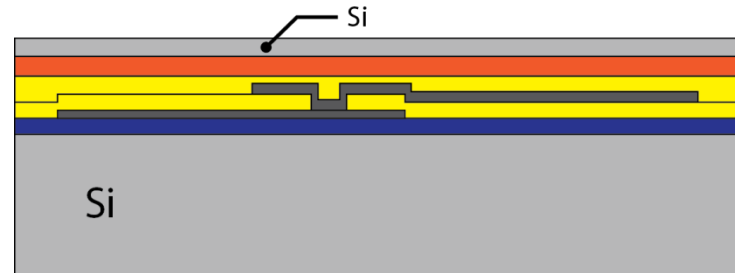
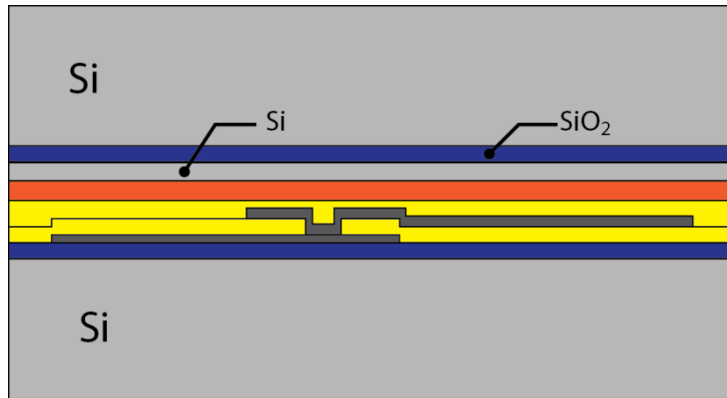
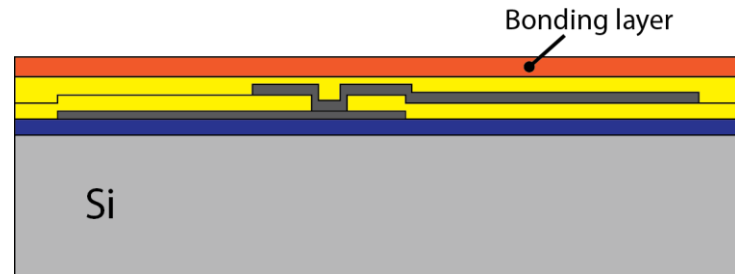
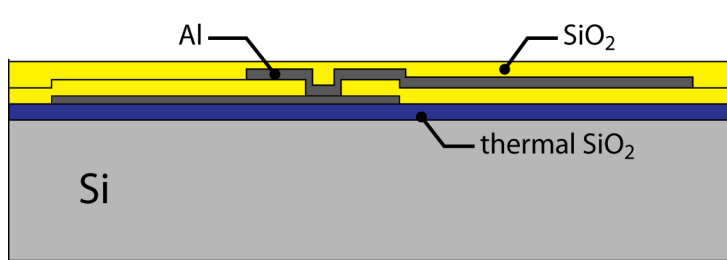
NEM switch on top of 2 metal layer interconnect wafer

## Method:

Metal anchors for mechanical stability and electrical connection

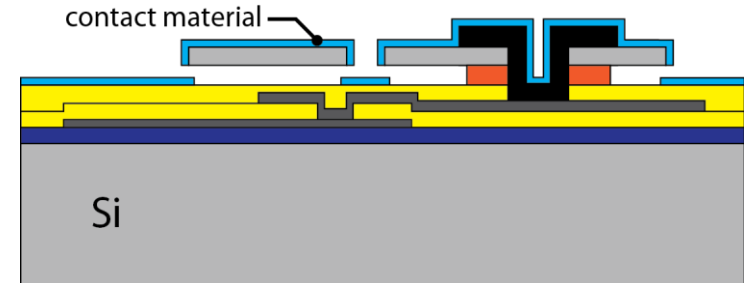
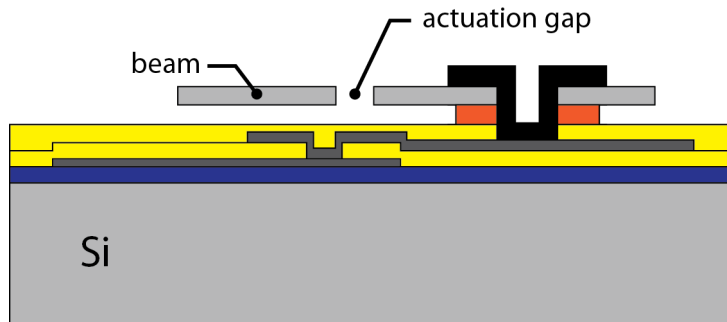
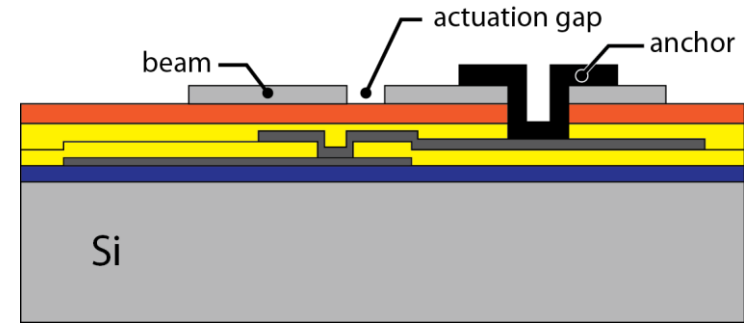
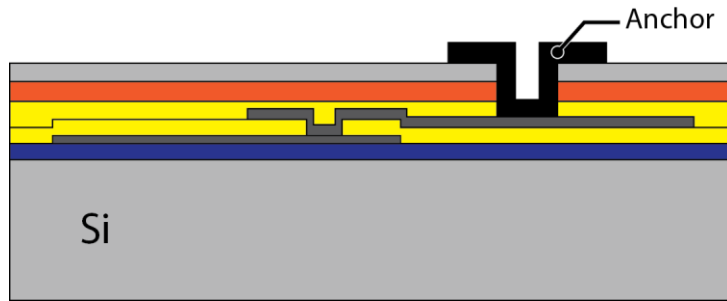


# Heterogeneous Integration Process





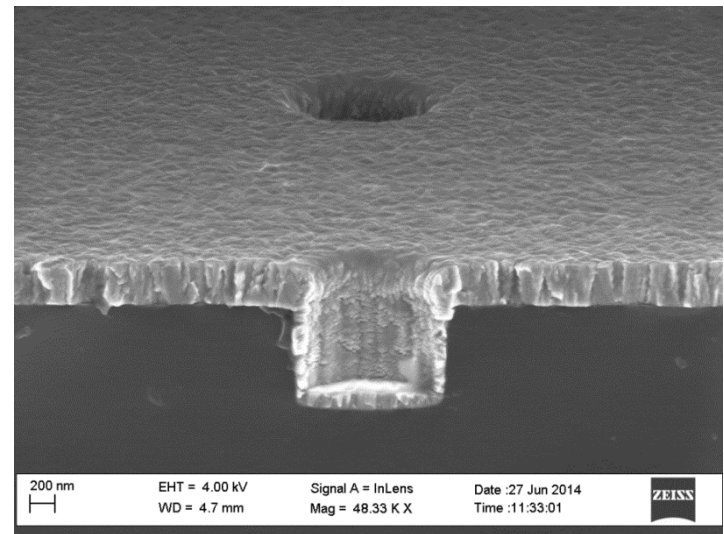
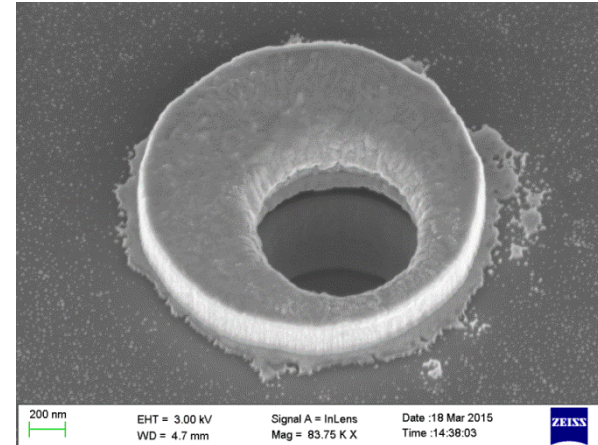
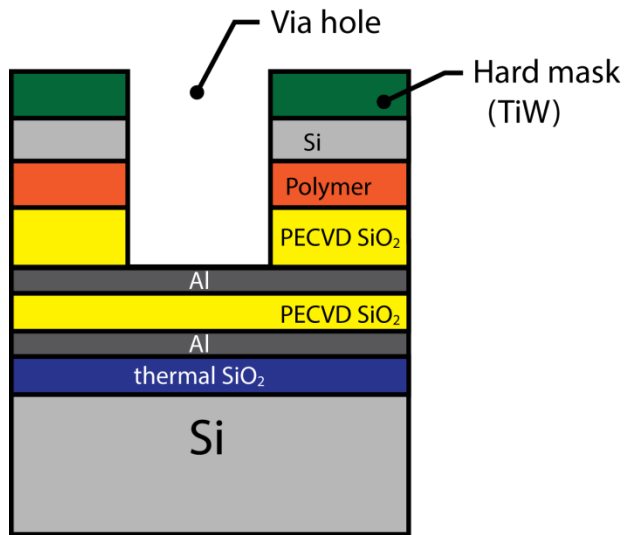
# Heterogeneous Integration Process



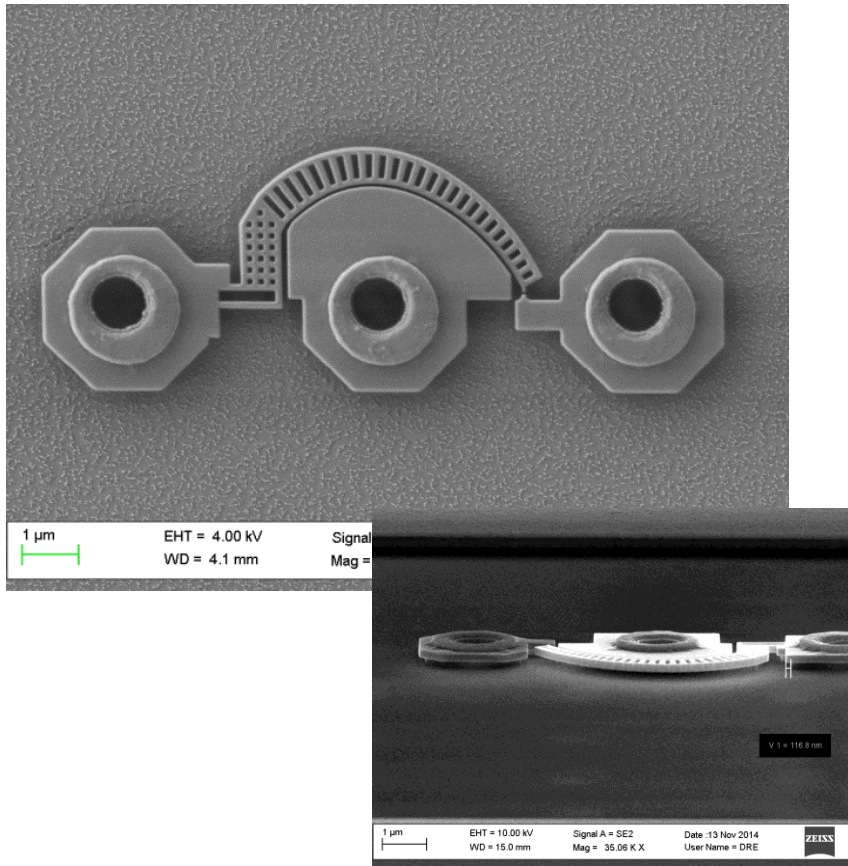
# Challenges

## Etching of Anchor holes

- Use hard mask to etch through different materials
- How do you know when to stop etching?



# Integrated Moni-Si NEM Switches

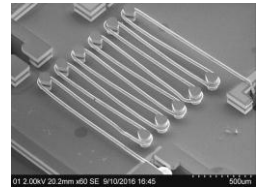


Qin, T., Bleiker, S. J., Rana, S., Niklaus, F., & Pamunuwa, D. (2018). Performance Analysis of Nanoelectromechanical Relay-Based Field-Programmable Gate Arrays. *IEEE Access*.

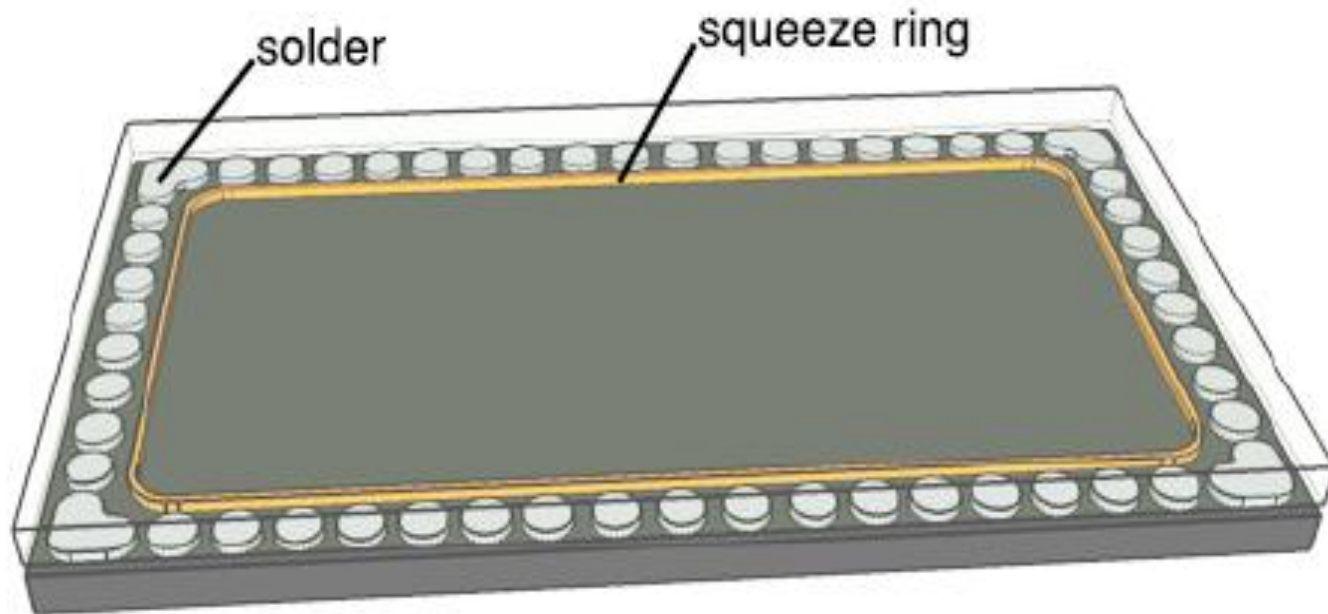


# *Research Topics in Group*

- Heterogeneous 3D Integration for MEMS & NEMS
- **Integration and Packaging for MEMS**
- Nanomanufacturing Technologies and Graphene NEMS

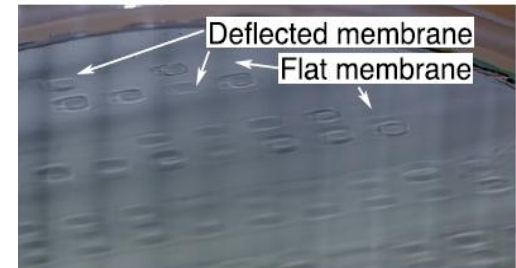
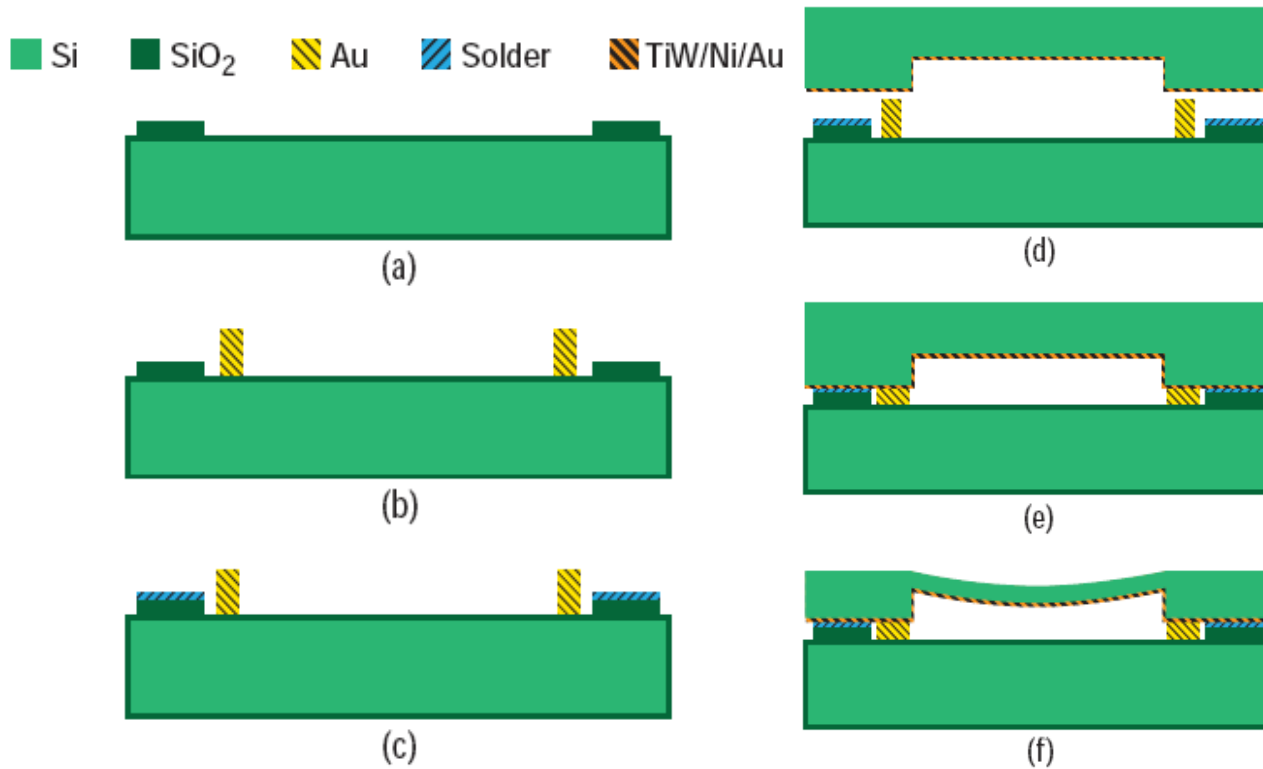


## Wafer-Level Vacuum Sealing Using Cold Metal Welding in Combination with Solder Bumps

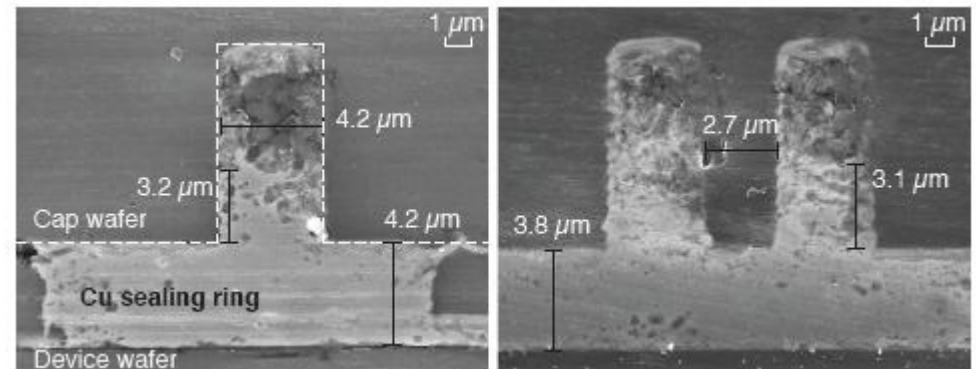
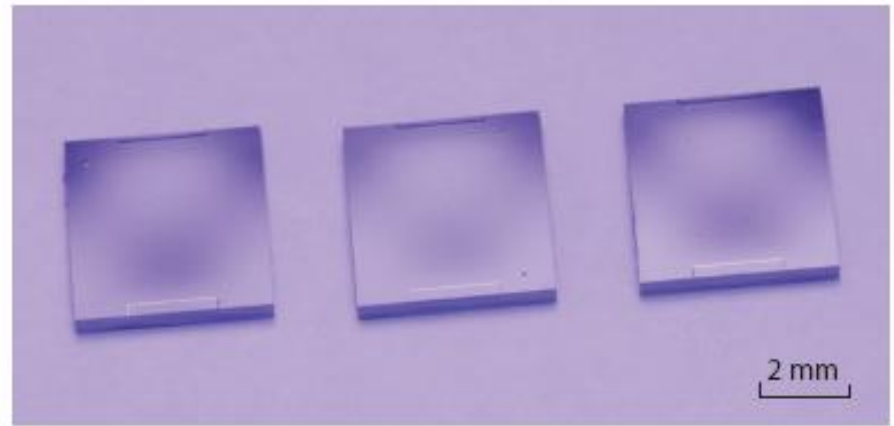
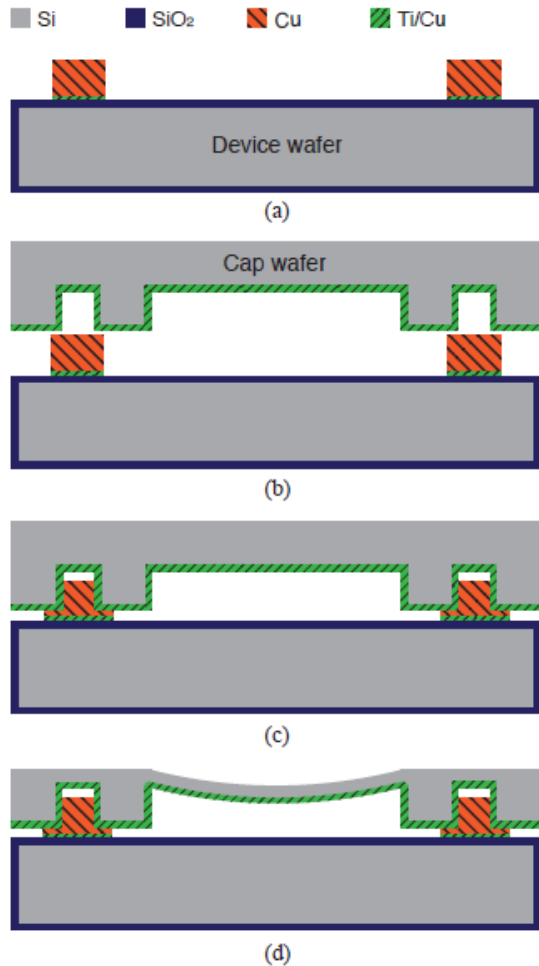


- Au sealing ring prevents solder vapour enter cavity.
- Solder bumps provide bond strength.

# Wafer-Level Vacuum Sealing: Process Flow

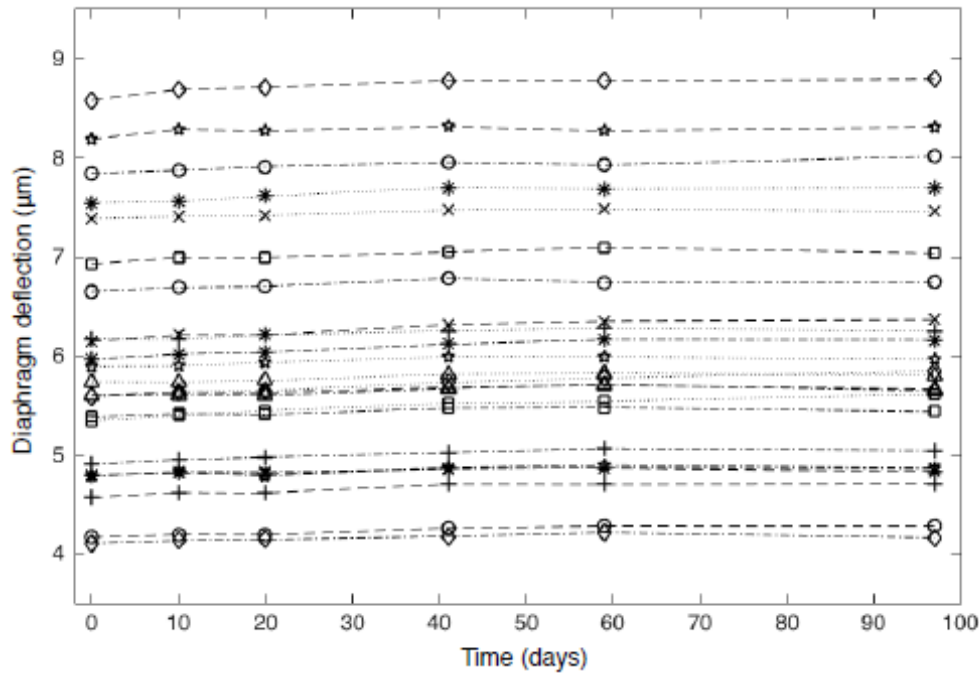


# Wafer-Level Low-Temperature Vacuum Sealing Using 8 $\mu\text{m}$ Wide Copper Rings





# Wafer-Level Low-Temperature Vacuum Sealing Using Copper Sealing

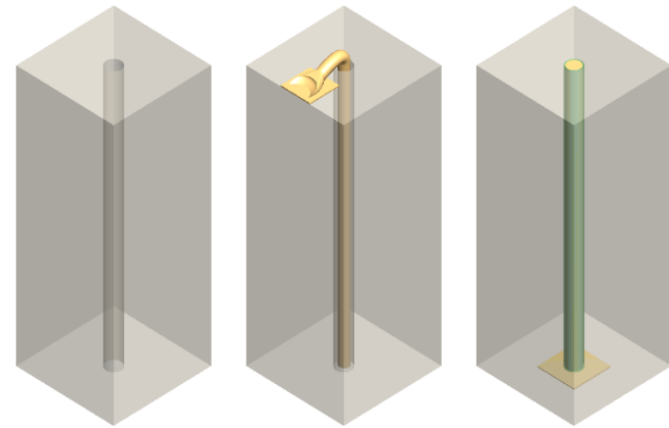


Gas	O2G2 design		O2G3 design	
	Pressure (mbar)	Percent (%)	Pressure (mbar)	Percent (%)
H <sub>2</sub>	$2.9 \times 10^{-2}$	63.07	0	0
CO <sub>2</sub>	$1.1 \times 10^{-2}$	23.92	0	0
CO	$5.1 \times 10^{-3}$	11.09	0	0
CH <sub>4</sub>	0	0	$2.5 \times 10^{-2}$	97.66
CH <sub>3</sub> <sup>a</sup>	$6.7 \times 10^{-4}$	1.46	$4.5 \times 10^{-4}$	1.76
Ar	$2.1 \times 10^{-4}$	0.46	$1.3 \times 10^{-4}$	0.51
He	0	0	$1.8 \times 10^{-5}$	0.07
O <sub>2</sub>	0	0	0	0
N <sub>2</sub>	0	0	0	0
H <sub>2</sub> O	0	0	0	0
<b>Total</b>	$4.6 \times 10^{-2}$	100.00	$2.6 \times 10^{-2}$	100.00

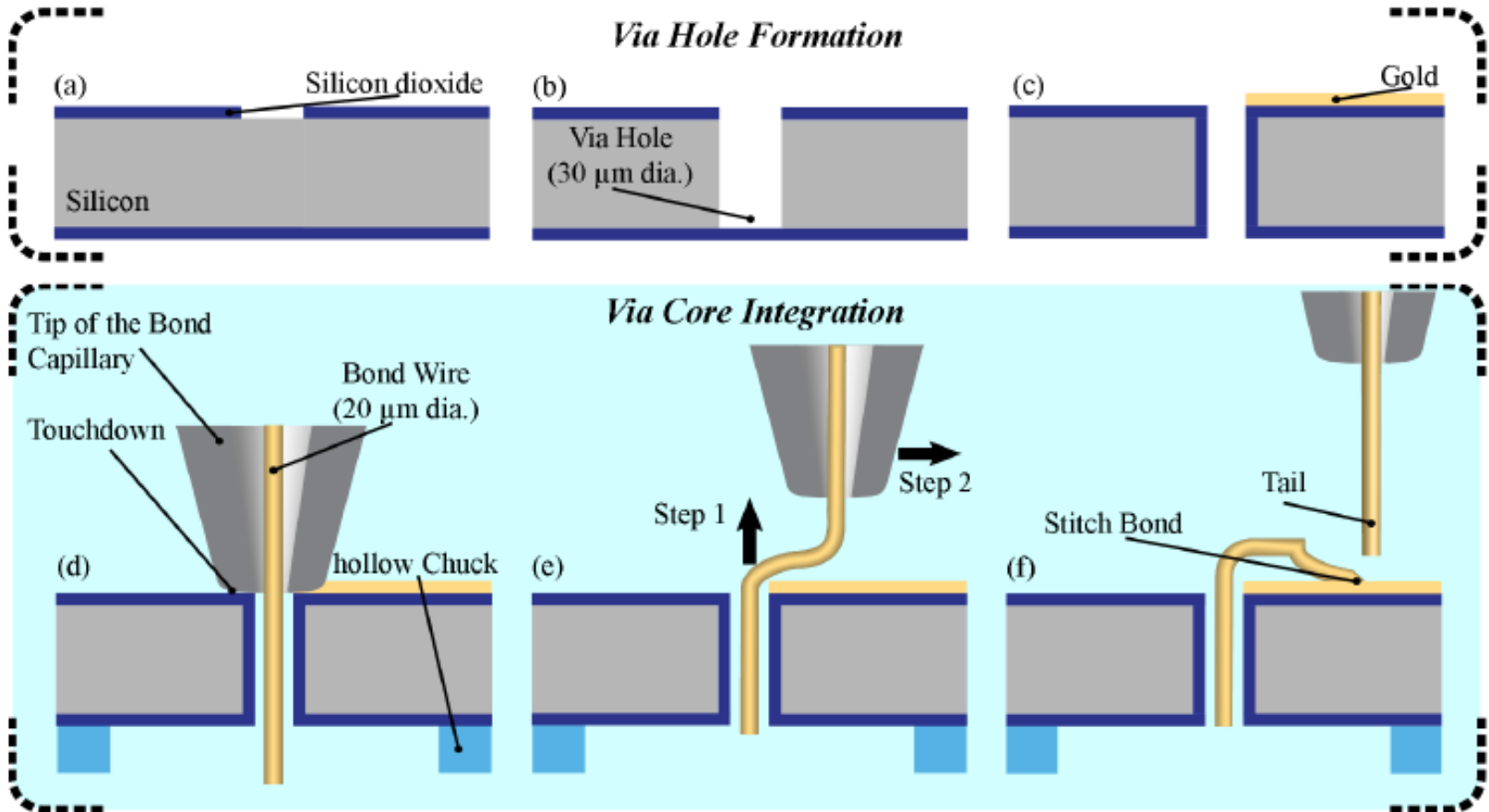


# Wire Bonded TSVs

- Low-cost for low to medium TSV density
- Enable high aspect ratio TSV formation
- No lithography (mask-less) TSV formation
- Low temperature budget approach

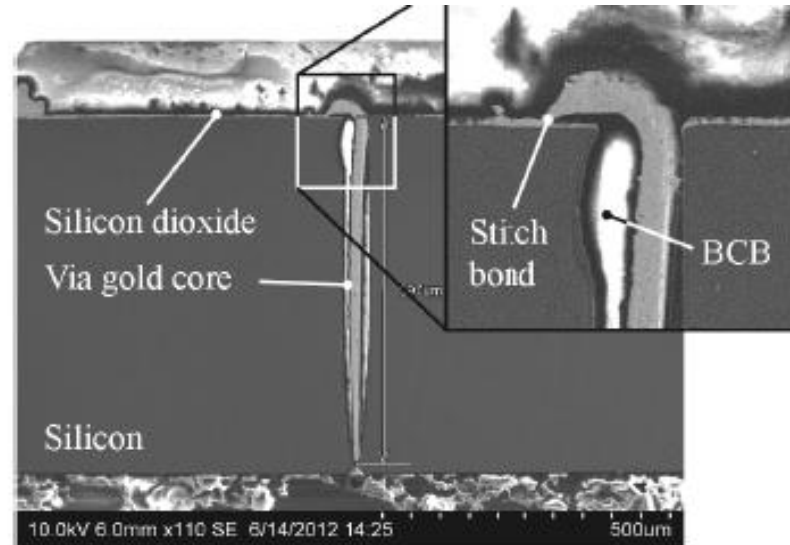
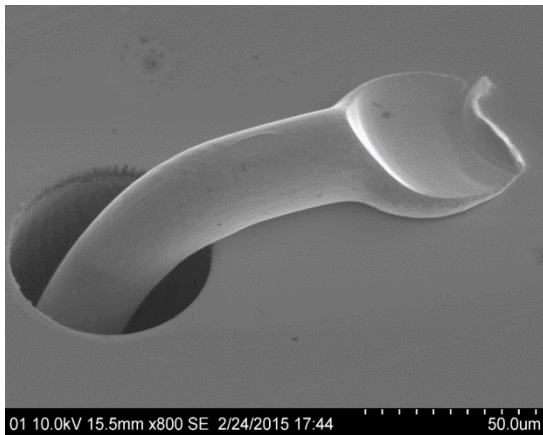
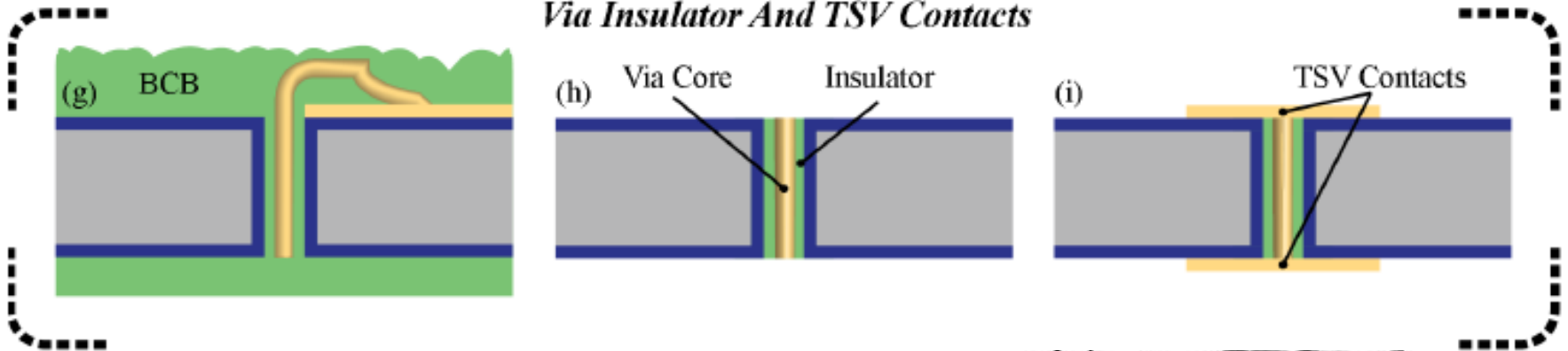


# TSVs Manufacturing Using Wire Bonding

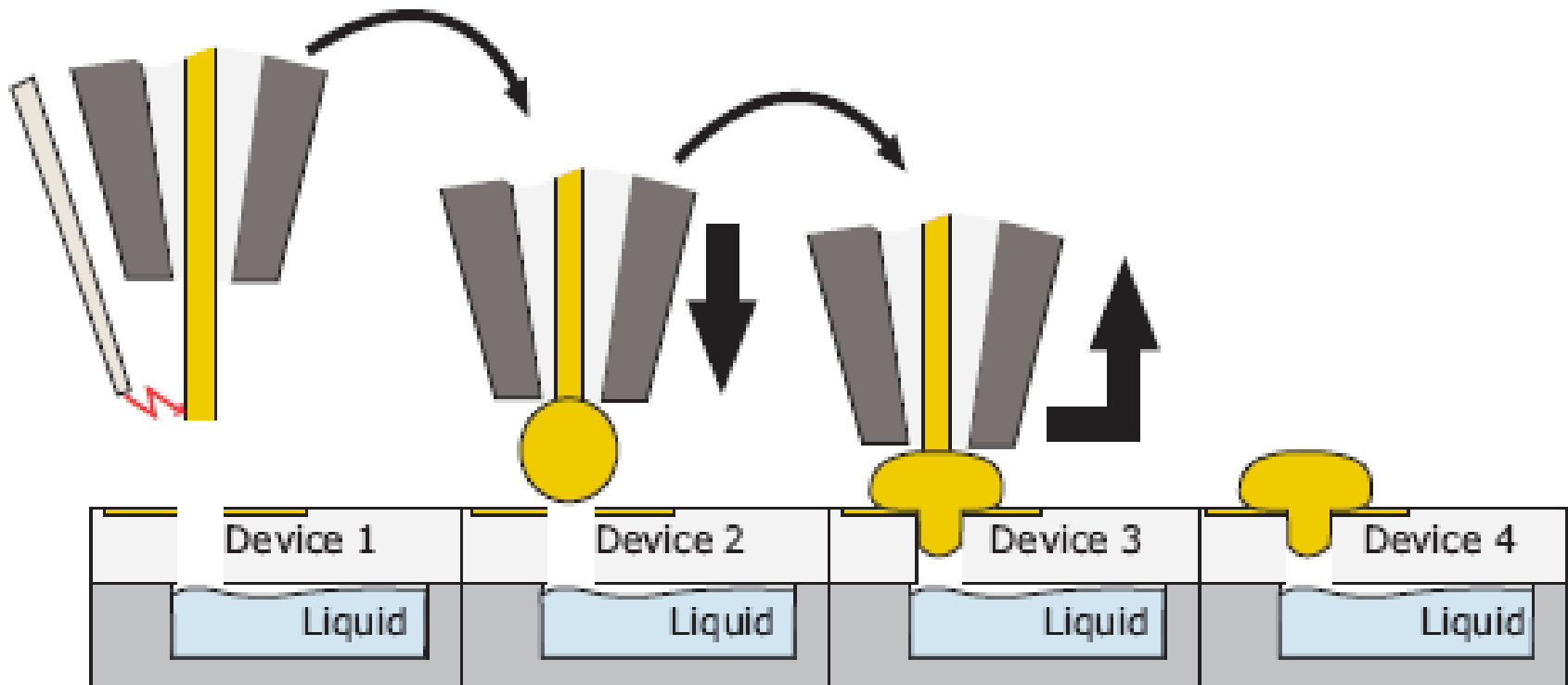


# Gold TSVs with Aspect Ratios > 20

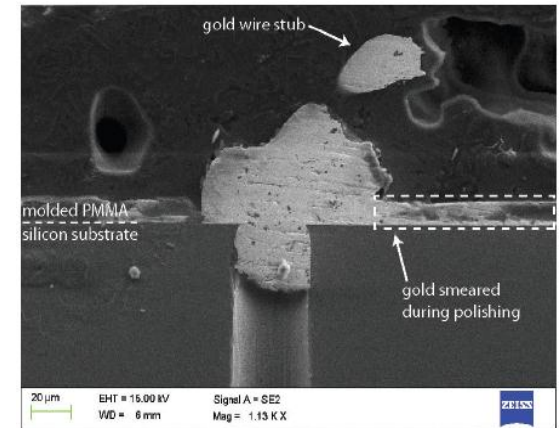
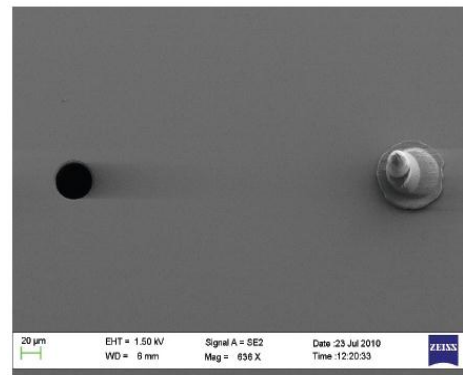
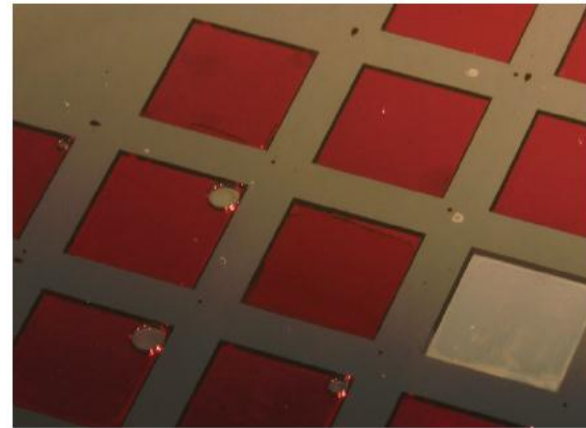
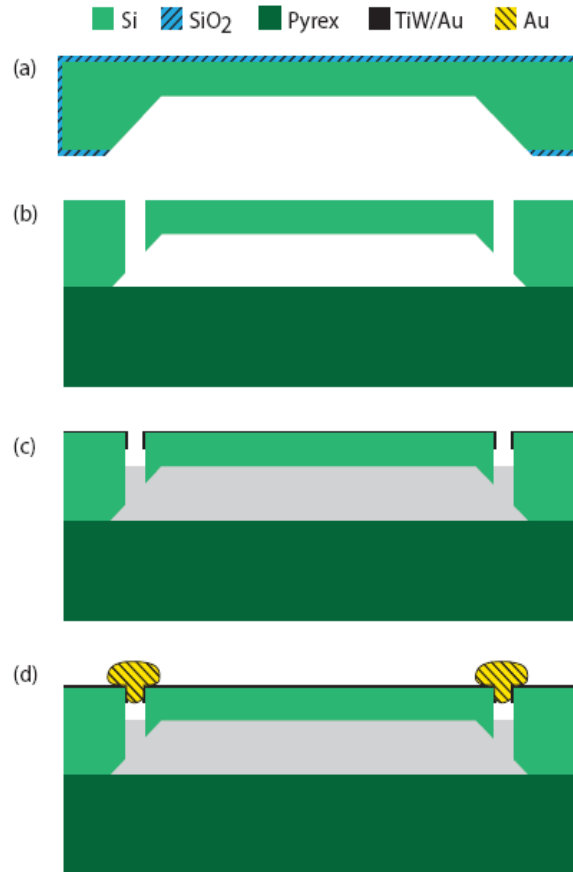
*Via Insulator And TSV Contacts*



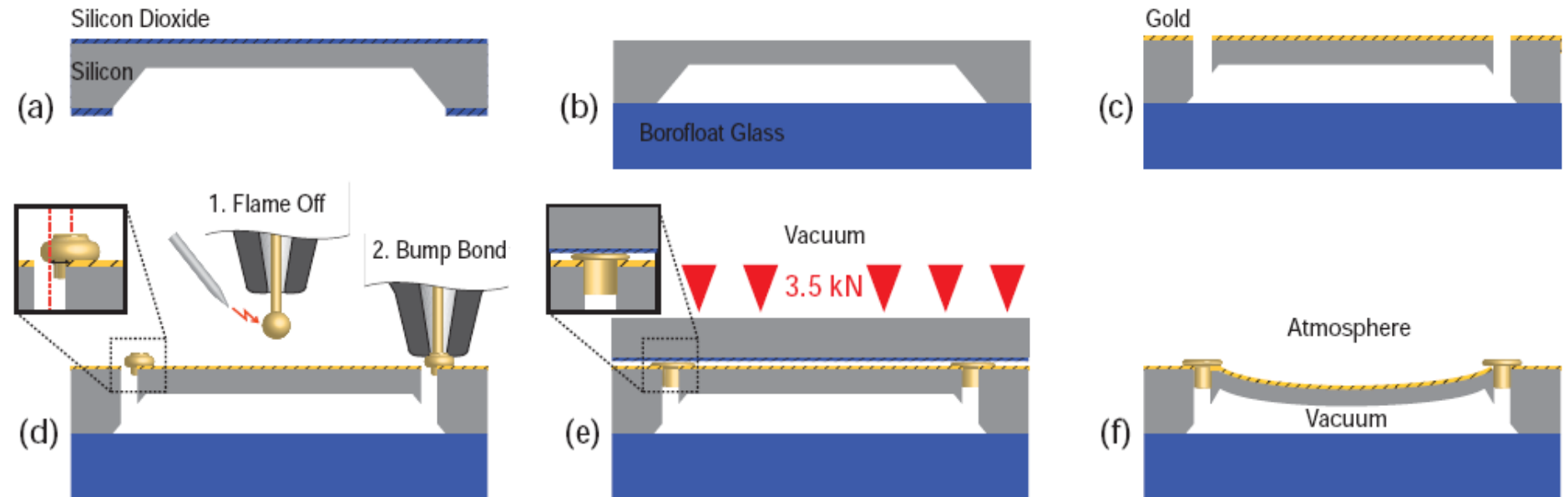
# Sealing of Liquids in MEMS Cavities Using Cold Metal Plugging



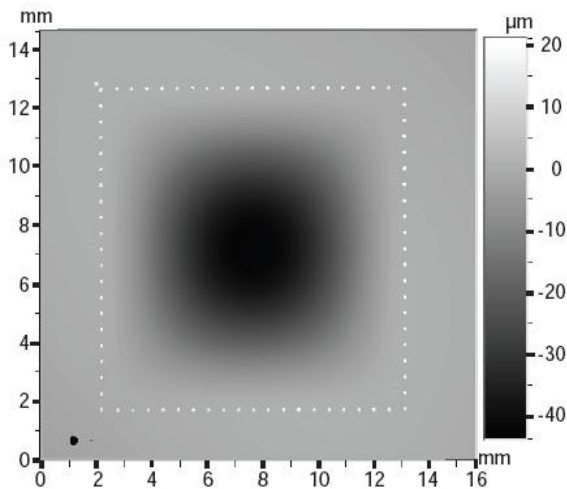
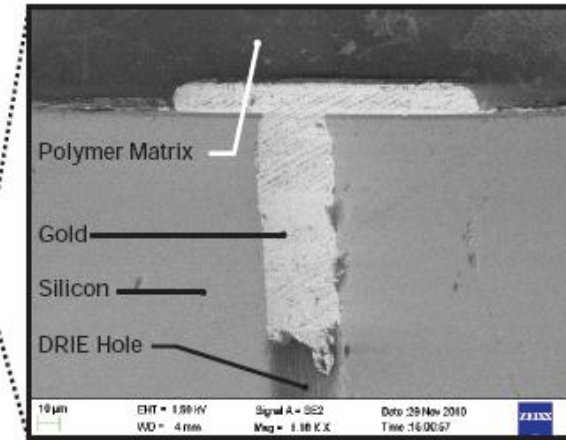
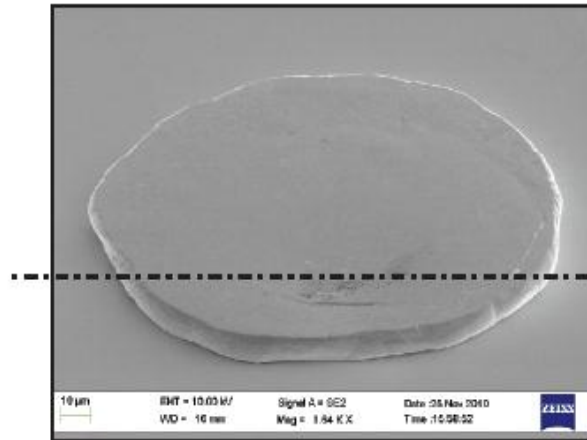
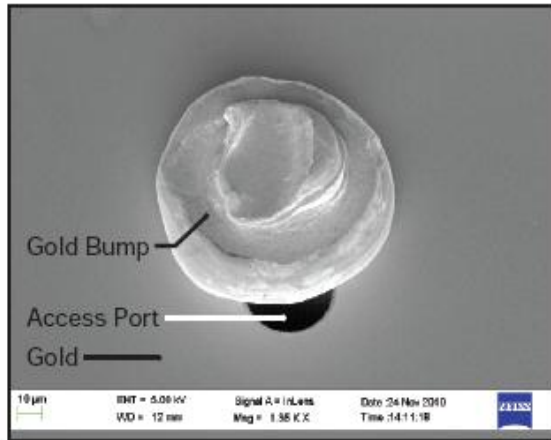
# Sealing of Liquids in MEMS Cavities Using Cold Metal Plugging



# Wafer-Level Vacuum Sealing Using Cold Metal Plugging



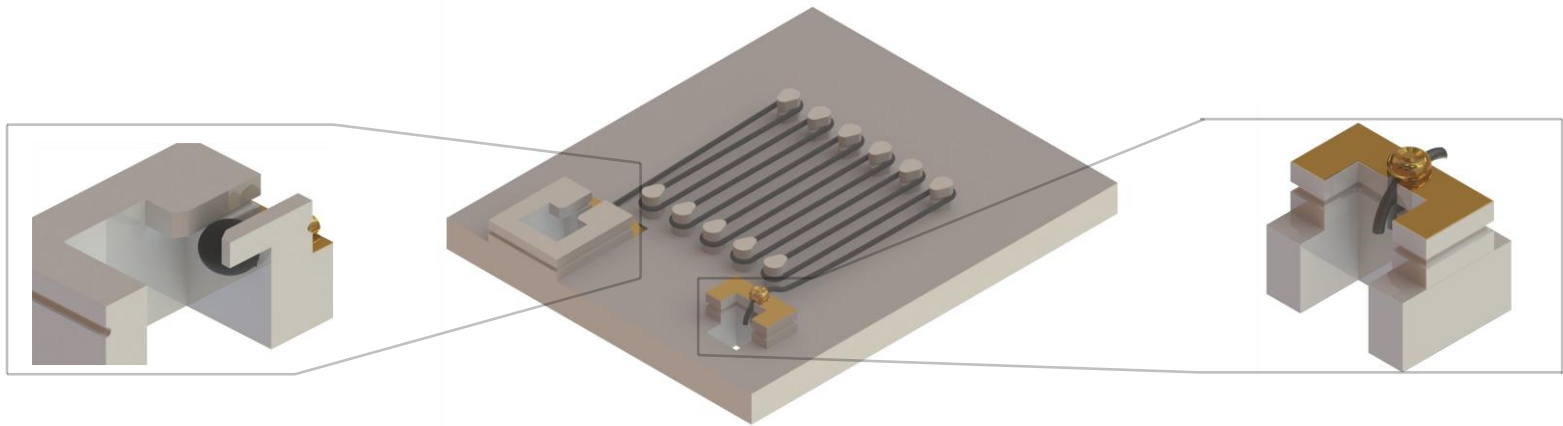
# Wafer-Level Vacuum Sealing Using Cold Metal Plugging



Gas	Pressure, 2 ports		Pressure, 80 ports	
	[mbar]	%	[mbar]	%
H <sub>2</sub> O	$3.33 \times 10^{-3}$	56.96 <sup>a</sup>	0	0
Ar	$1.00 \times 10^{-3}$	17.17	$6.15 \times 10^{-4}$	75.11
N <sub>2</sub>	$8.52 \times 10^{-4}$	14.56	0	0
H <sub>2</sub>	$5.25 \times 10^{-4}$	8.97	0	0
CH <sub>4</sub>	$8.75 \times 10^{-5}$	1.50	0	0
O <sub>2</sub>	$2.77 \times 10^{-5}$	0.47	0	0
CO <sub>2</sub>	$2.18 \times 10^{-5}$	0.37	$2.04 \times 10^{-4}$	24.86
He	0	0	$1.89 \times 10^{-7}$	0.02
Ne	0	0	0	0
C <sub>2</sub> H <sub>6</sub>	0	0	0	0
C <sub>3</sub> H <sub>8</sub>	0	0	0	0
CO	0	0	0	0
Kr	0	0	0	0
Total	$5.85 \times 10^{-3}$	100.00	$8.19 \times 10^{-4}$	100.00

# Wire Bonded Infrared Emitter

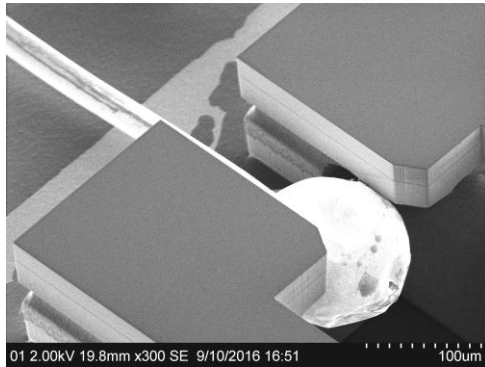
- Joule-heated suspended Kanthal filament
- Integration using an automated wire bonding tool
- Mechanical fixation and placement by
  - Attachment structures for free air ball & wire
  - Guiding posts



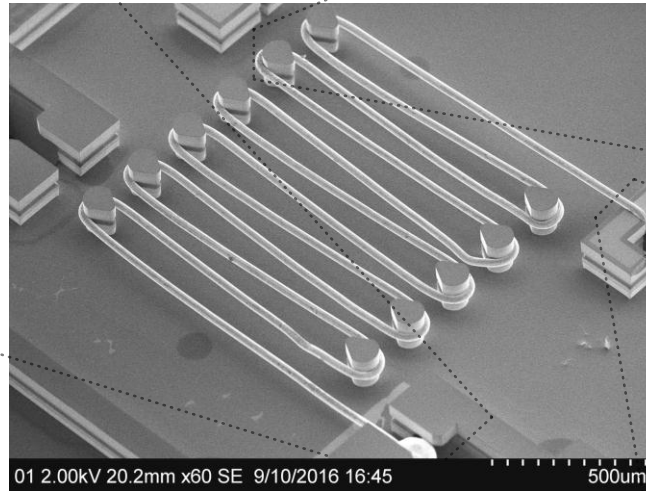


# Filament Integration Results

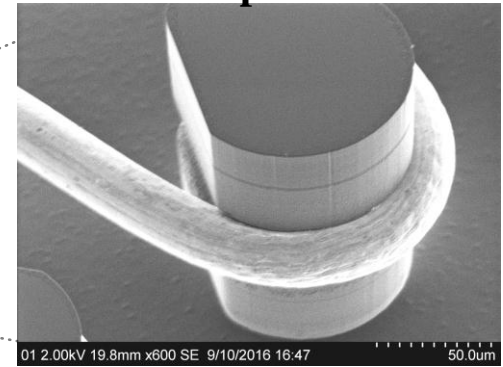
## 2. Free air ball attachment



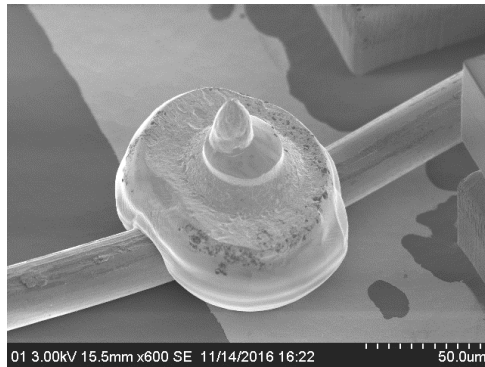
## 1. Filament Emitter



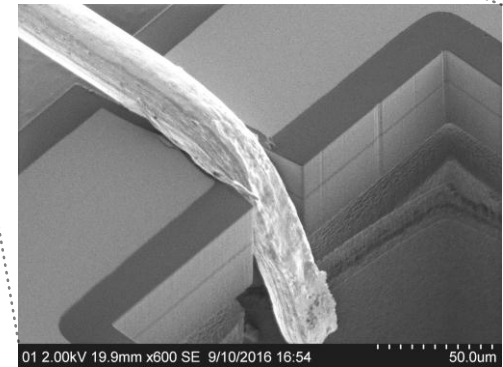
## 3. Filament placement



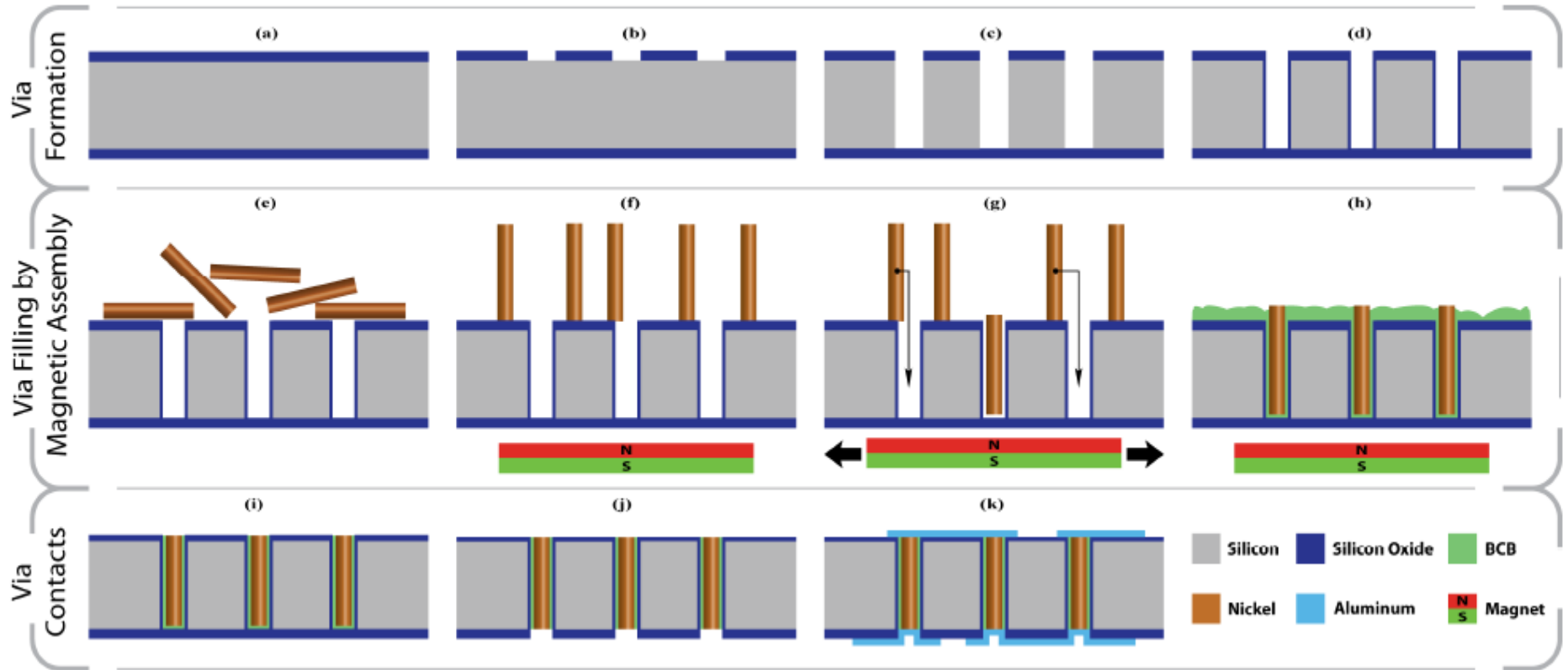
## 5. Electrical contact



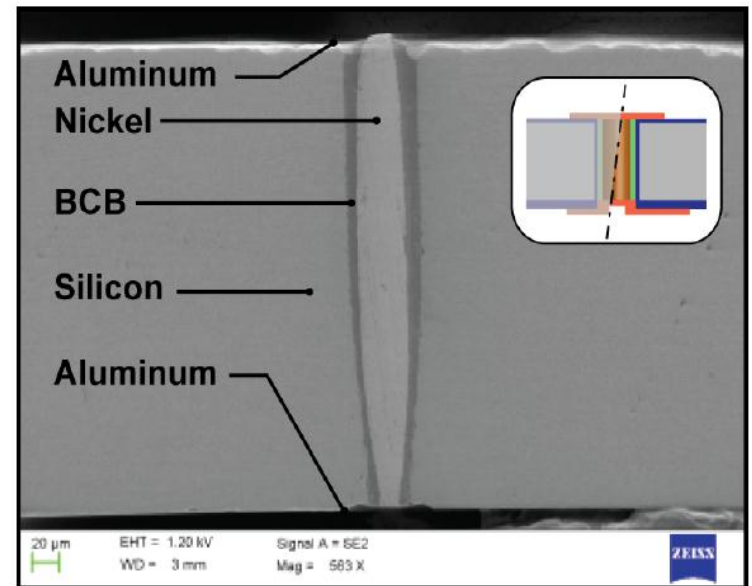
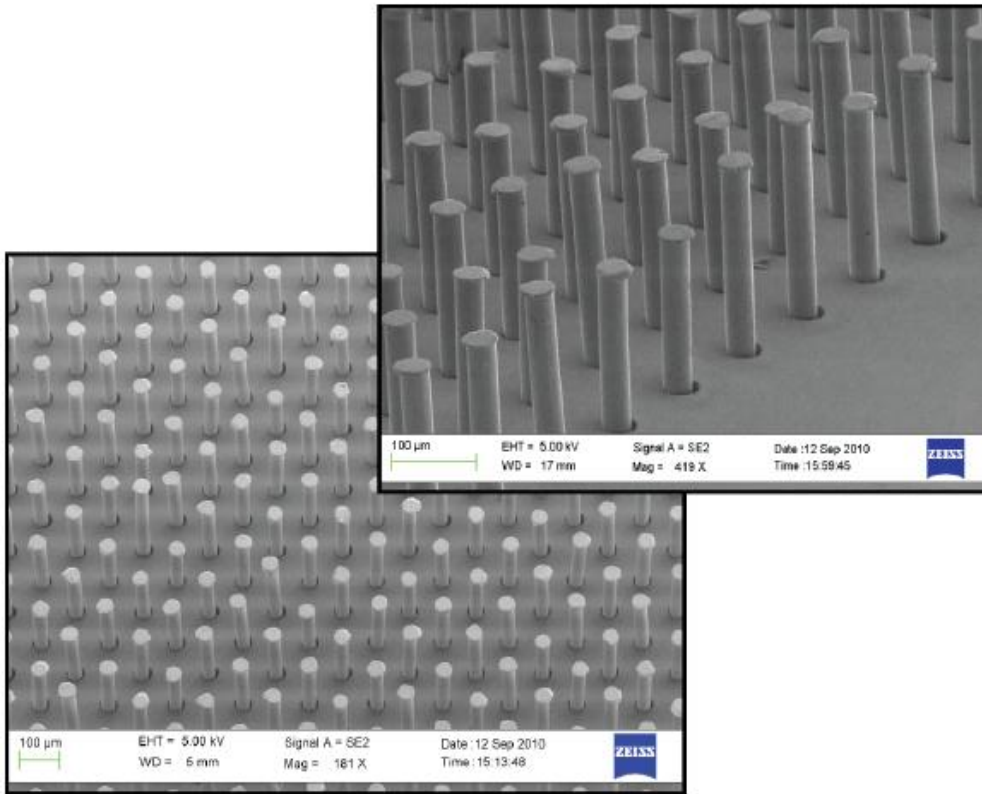
## 4. Filament attachment



# Fabrication of High-Aspect Ratio TSVs by Magnetic Assembly of Metal Studs



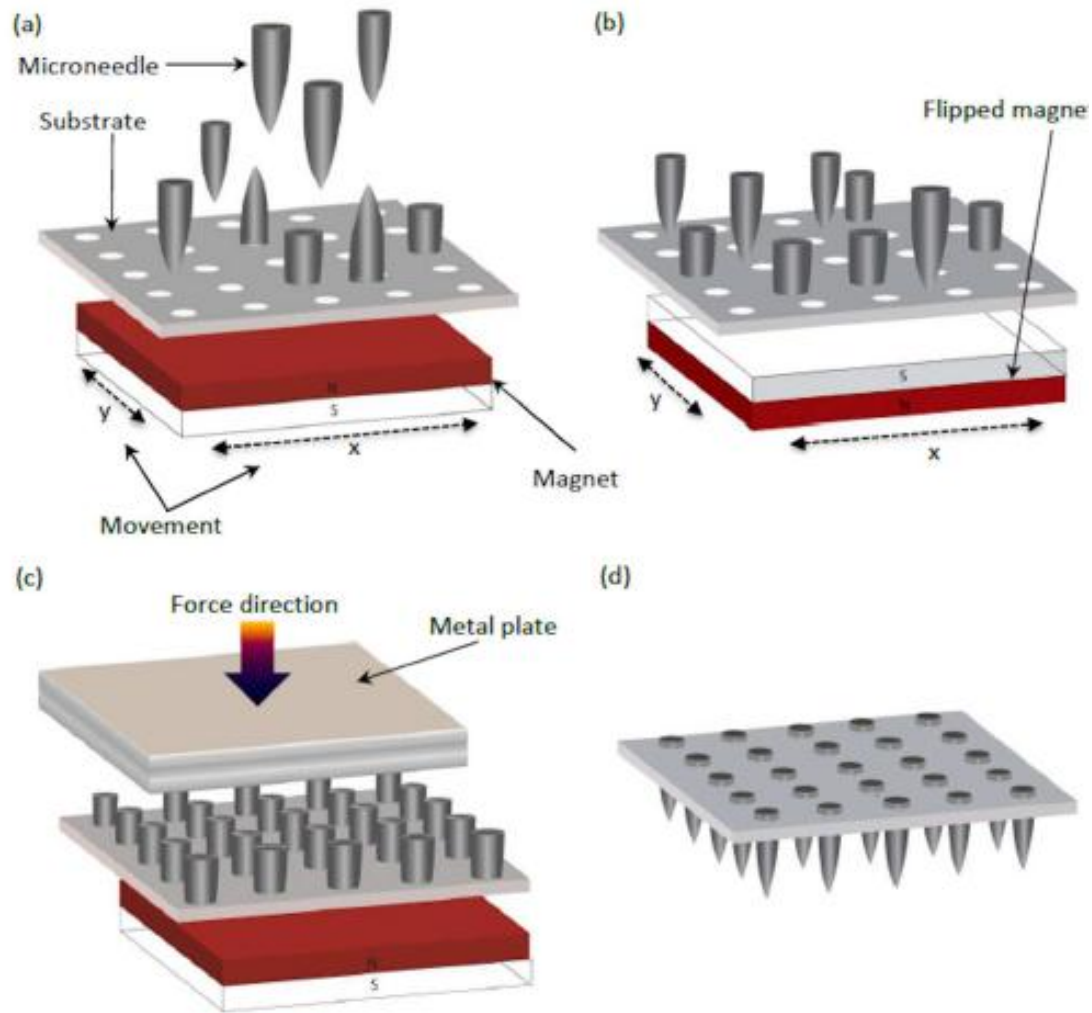
# High-Aspect Ratio Nickel TSVs





# Robotic Magnetic Self-assembly of TSVs

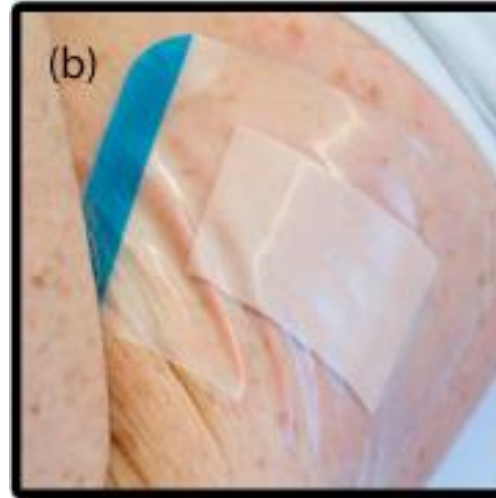
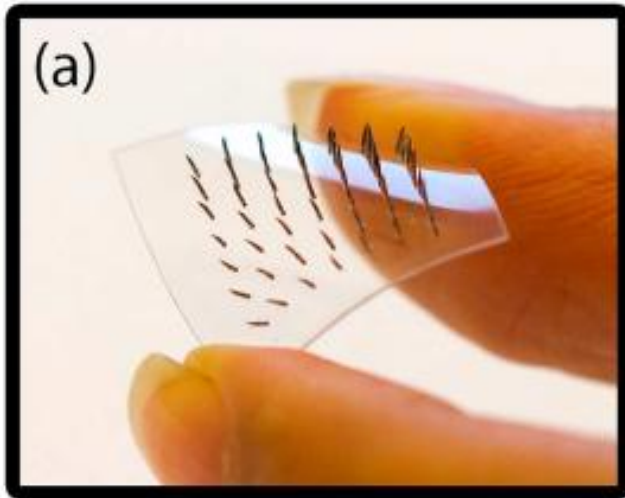
# Magnetic Self-assembly for Stretchable Microneedle Patches



# Magnetic Self-assembly for Stretchable Microneedle Patches

Combination of :

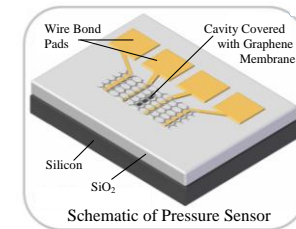
**Stretchable and flexible substrate for comfort; and  
Sharp and stiff needles for reliable penetration**





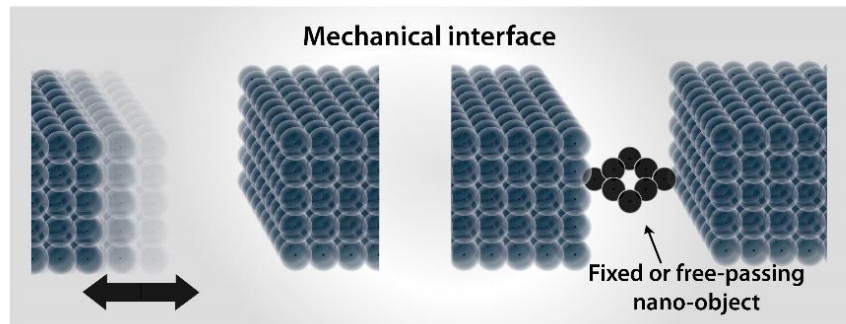
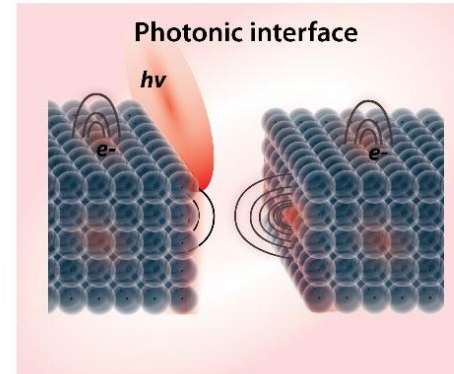
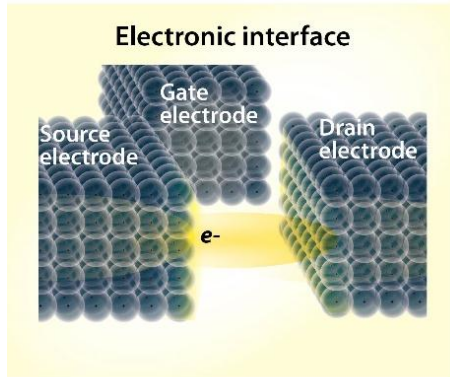
# *Research Topics in Group*

- Heterogeneous 3D Integration for MEMS & NEMS
- Integration and Packaging for MEMS
- **Nanomanufacturing Technologies and Graphene NEMS**





# Nanogap Electrodes

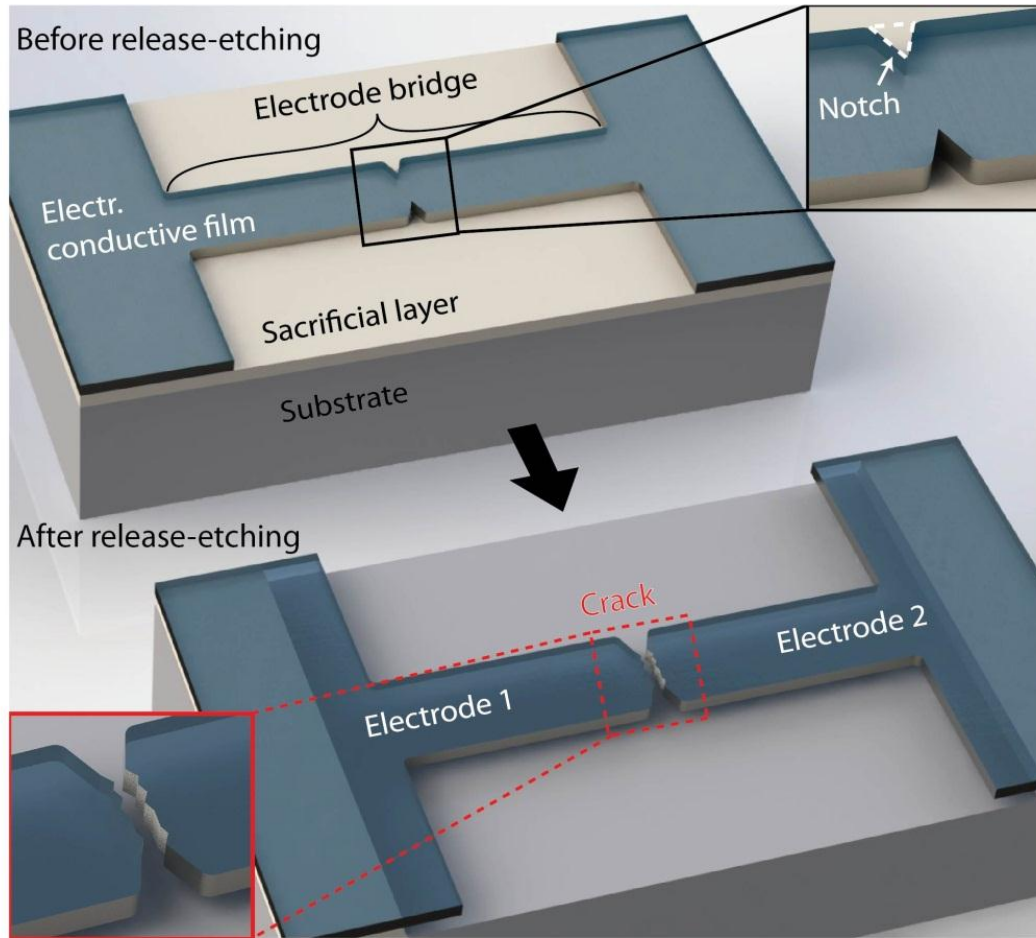


Nanogap electronics:  
Require sub-3 nm wide gaps between electrodes !

Major problem: Extremely difficult to realize



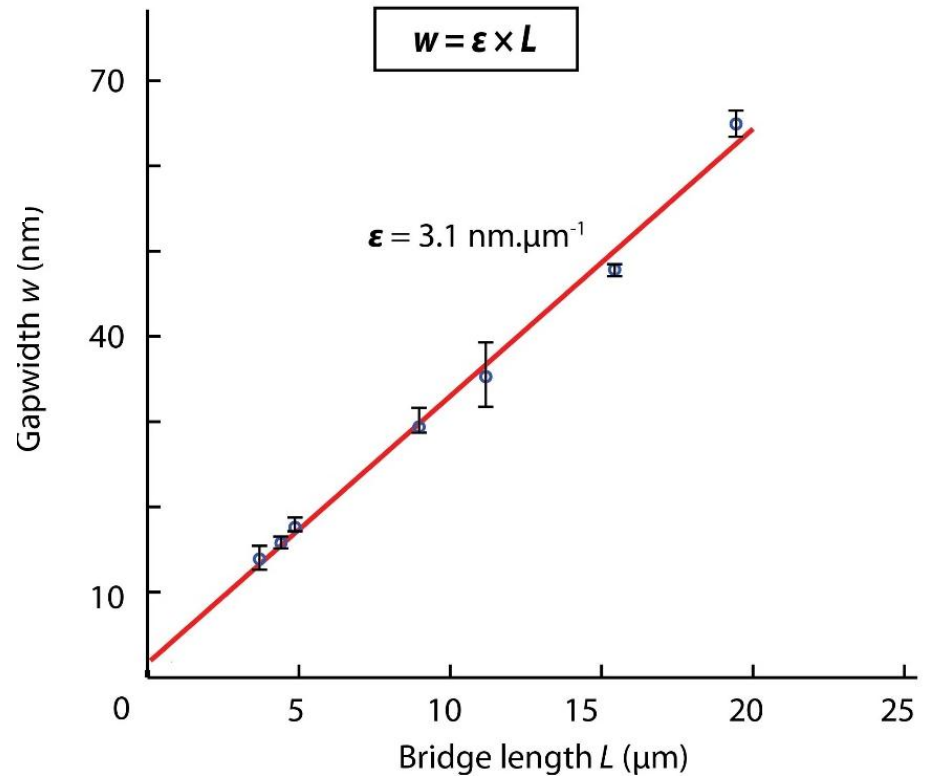
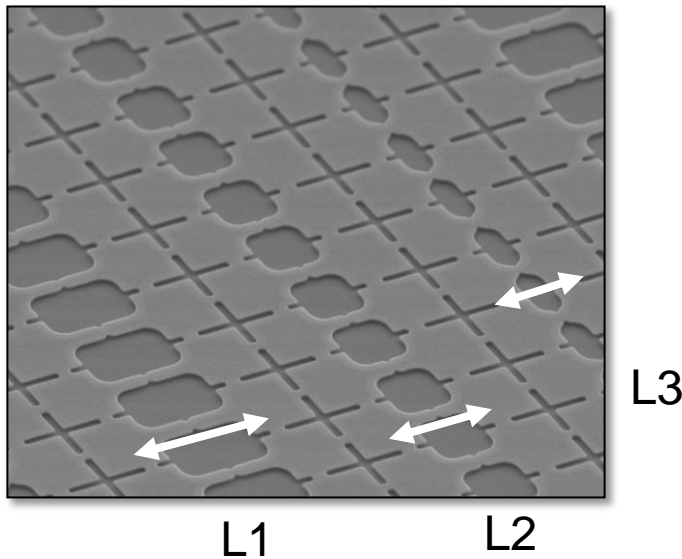
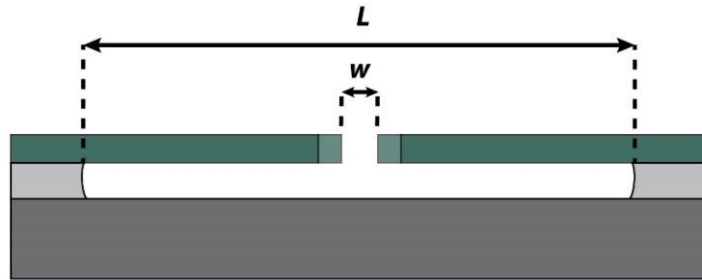
# Scalable Fabrication of Crack-Defined Nanogap Electrodes



- Control of gap size: 1-100 nm
- Realization of tunneling junctions
- Massively parallel fabrication

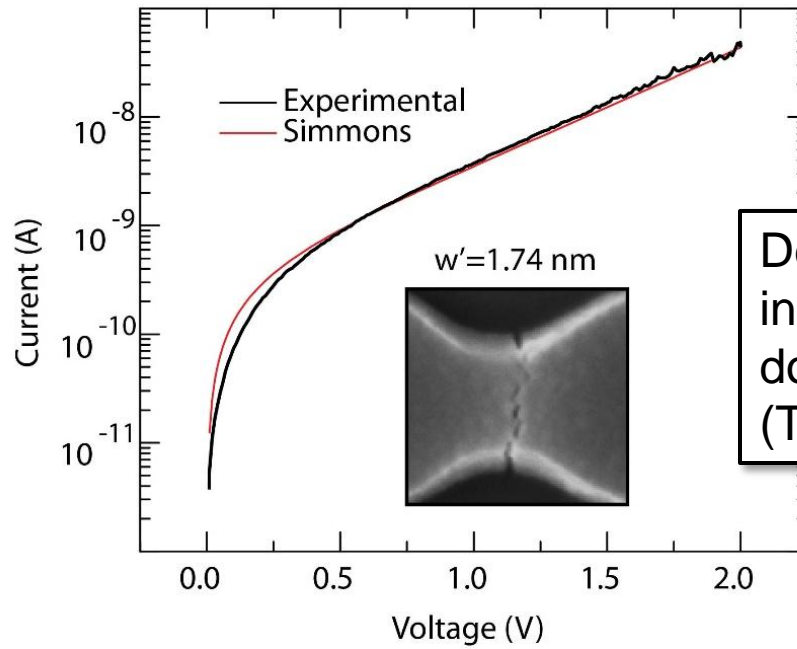
# Control of Gap Size

1  $\mu\text{m}$  in electrode bridge length  $\longleftrightarrow$  3.1 nm in nanogap width



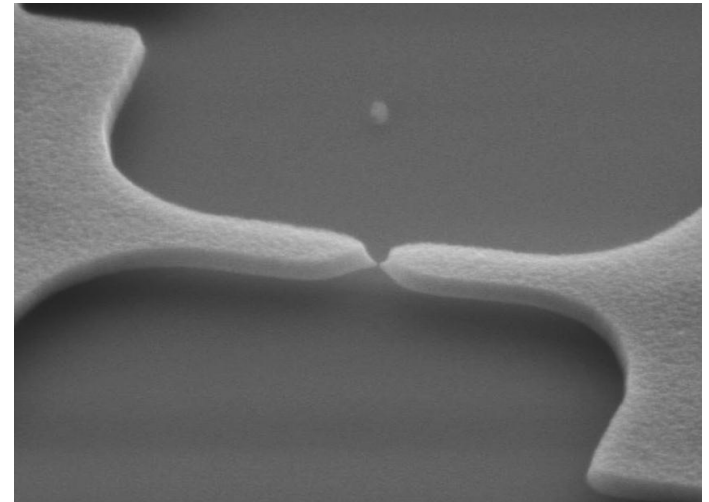
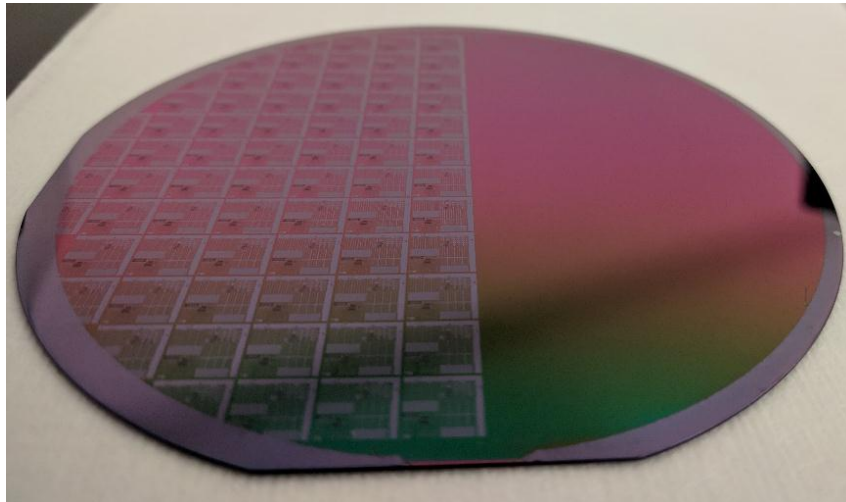
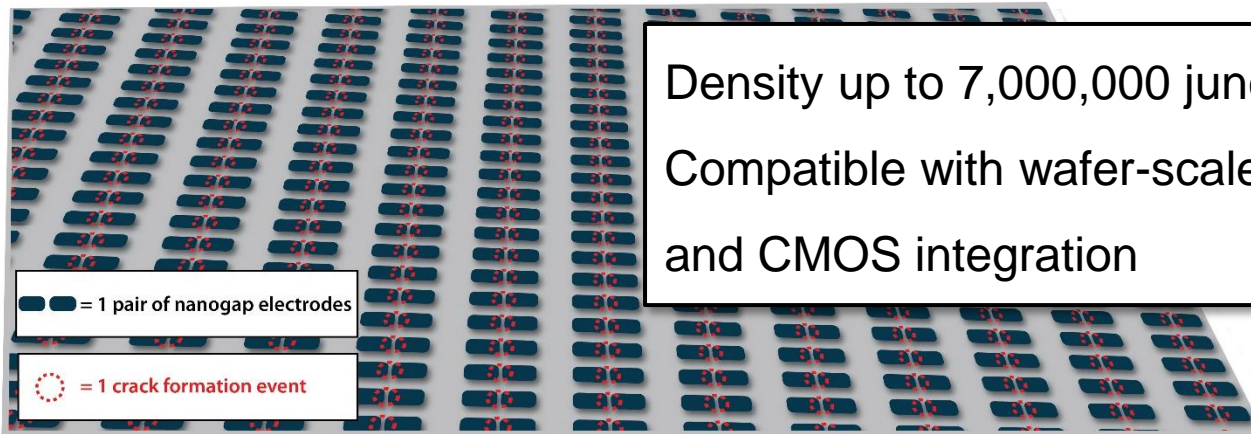
# Nanogap Tunneling Junctions

Electron quantum tunneling occurs with **sub-3 nm nanogaps**

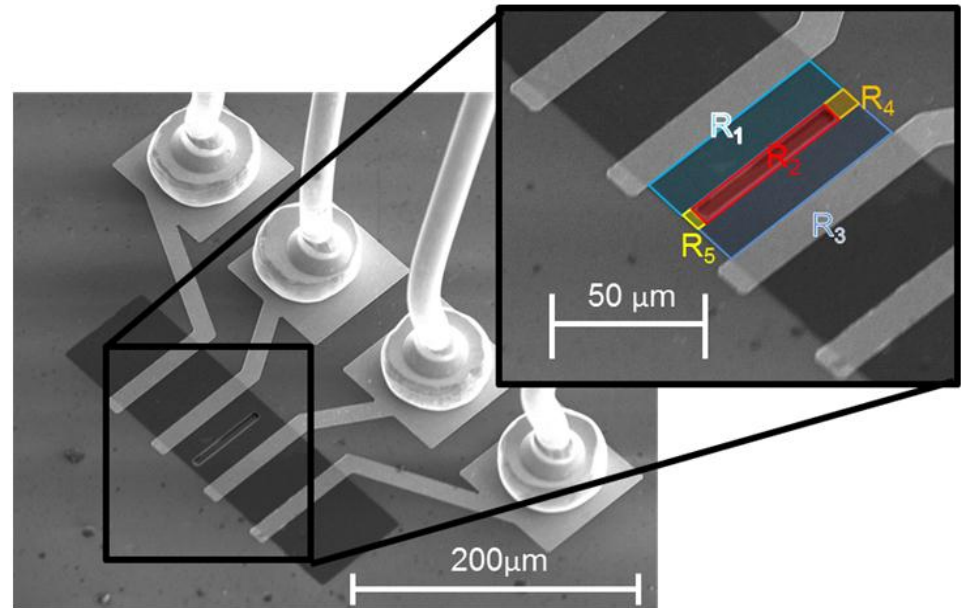
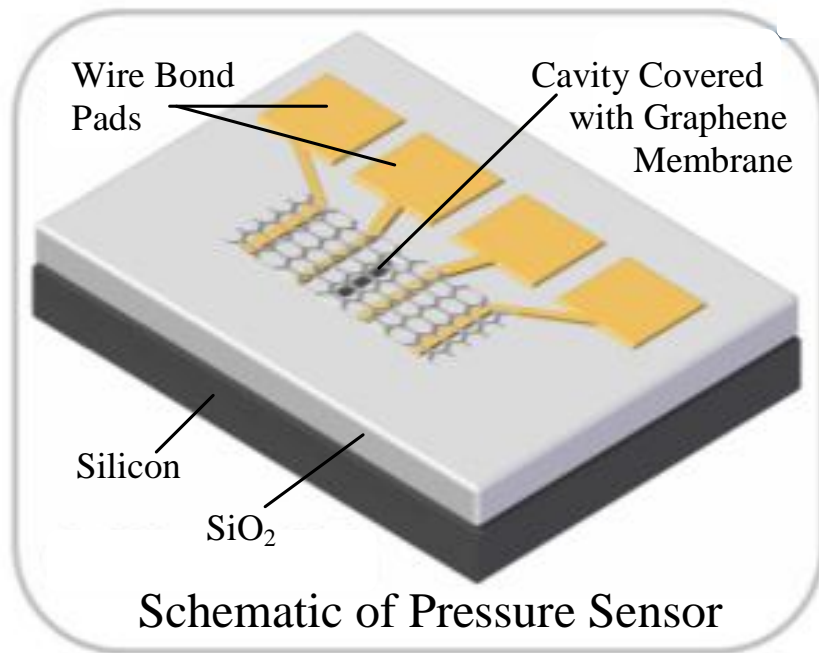


Demonstration of quantum tunneling in crack-defined nanogap electrodes down to **sub-1 nm** in titanium nitride (TiN) and gold (Au)

# Massively Parallel Fabrication

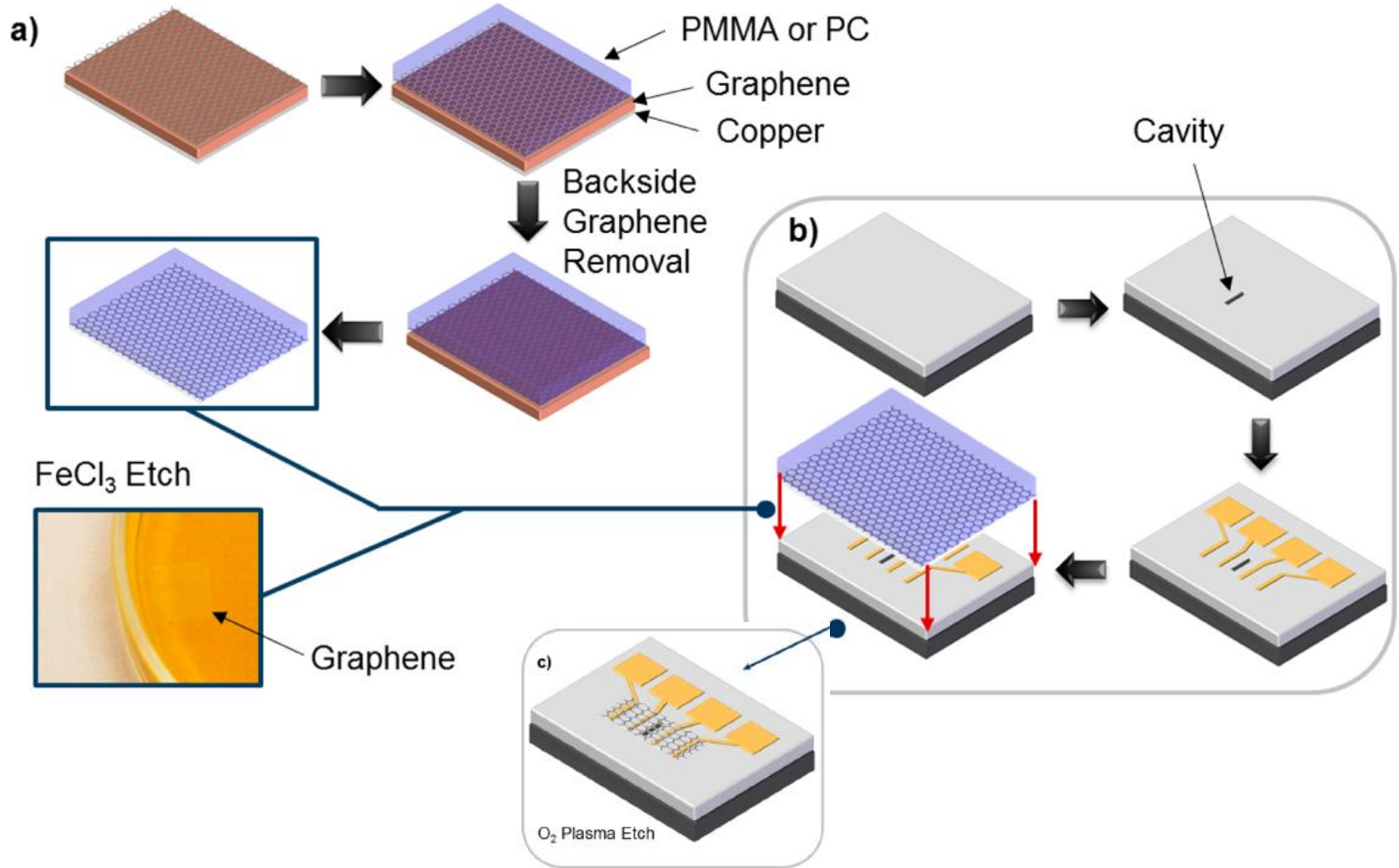


# Graphene-Based NEMS: Pressure Sensing

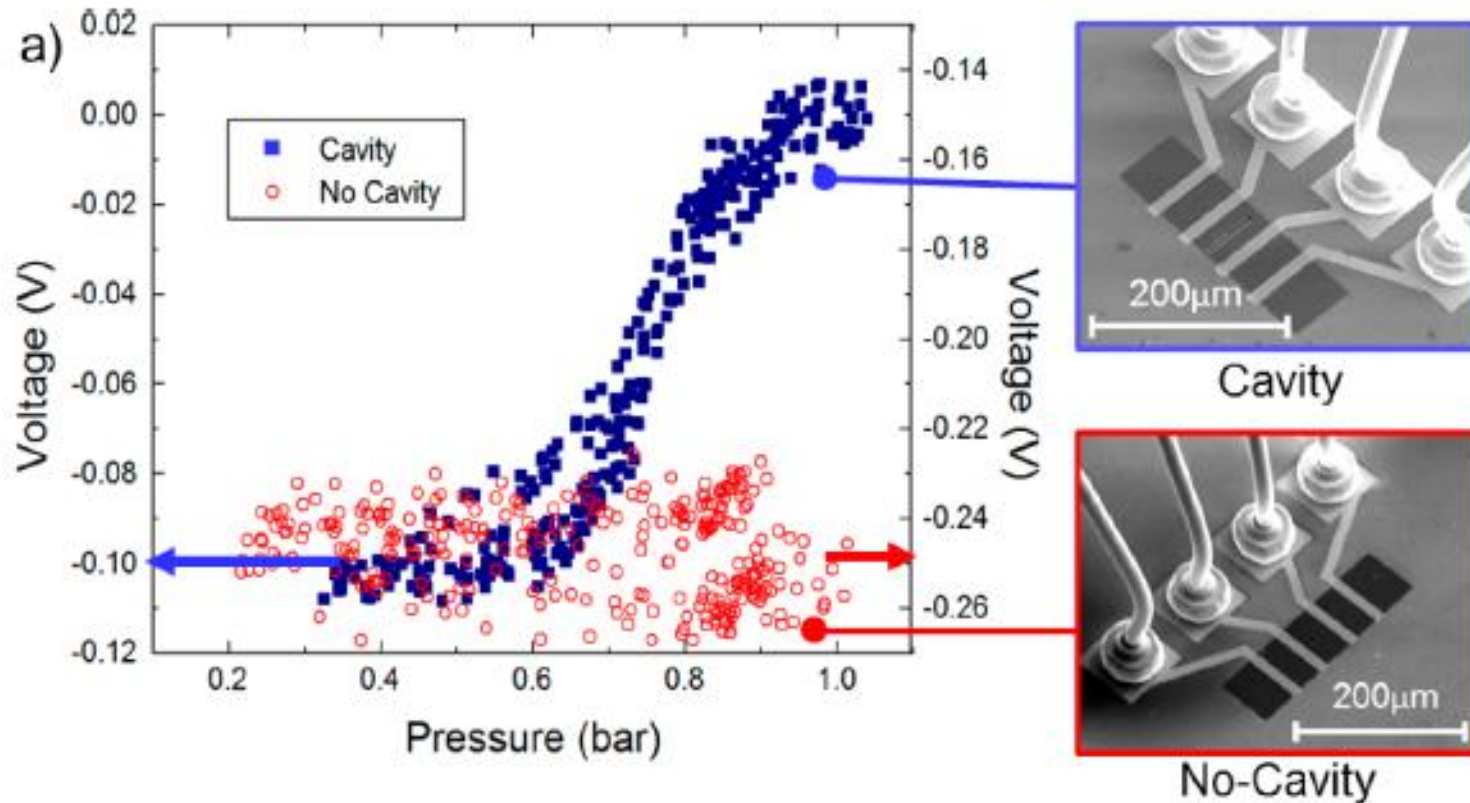




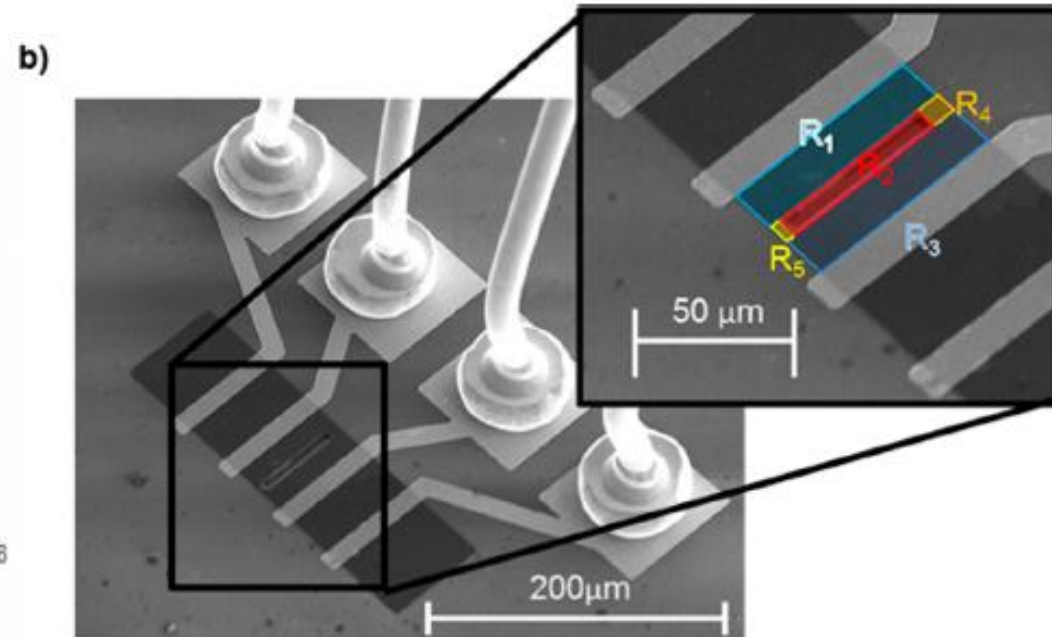
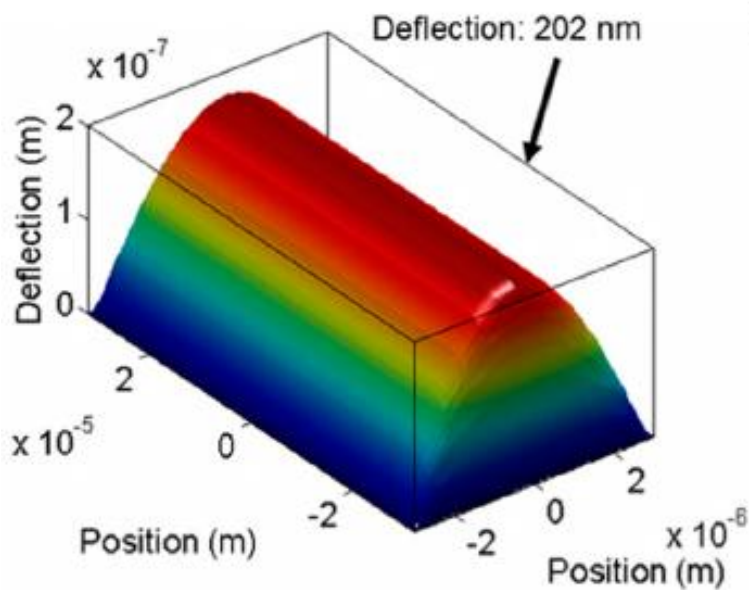
# Graphene-Integration in NEMS



# Graphene-NEMS Pressure Sensing



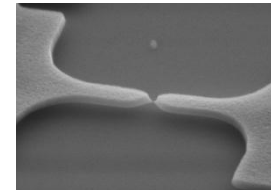
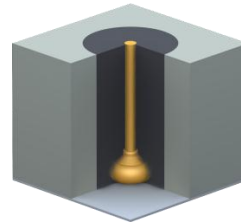
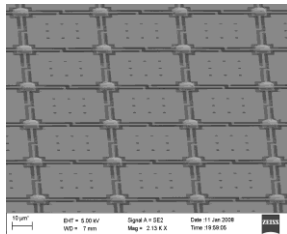
# Graphene-NEMS Pressure Sensing





# Summary

- **Heterogeneous 3D integration platform for micro-mirrors, IR bolometers and NEMS relays.**
- **Wafer-level vacuum packaging, and wire bonding and magnetic assembly for wire integration in MEMS.**
- **Graphene NEMS pressure sensors and nanofabrication technologies for tunnelling junctions.**





# Acknowledgements

## Funding Sources

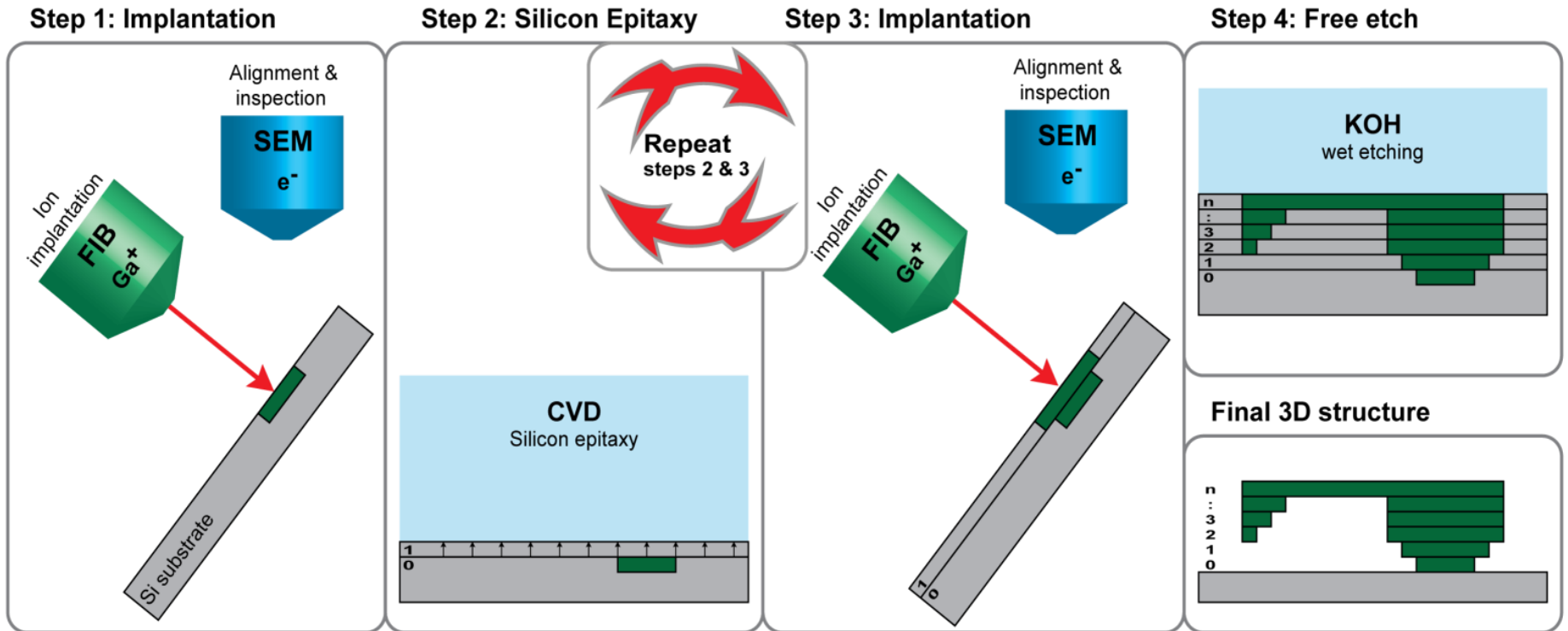


## Collaboration Partners

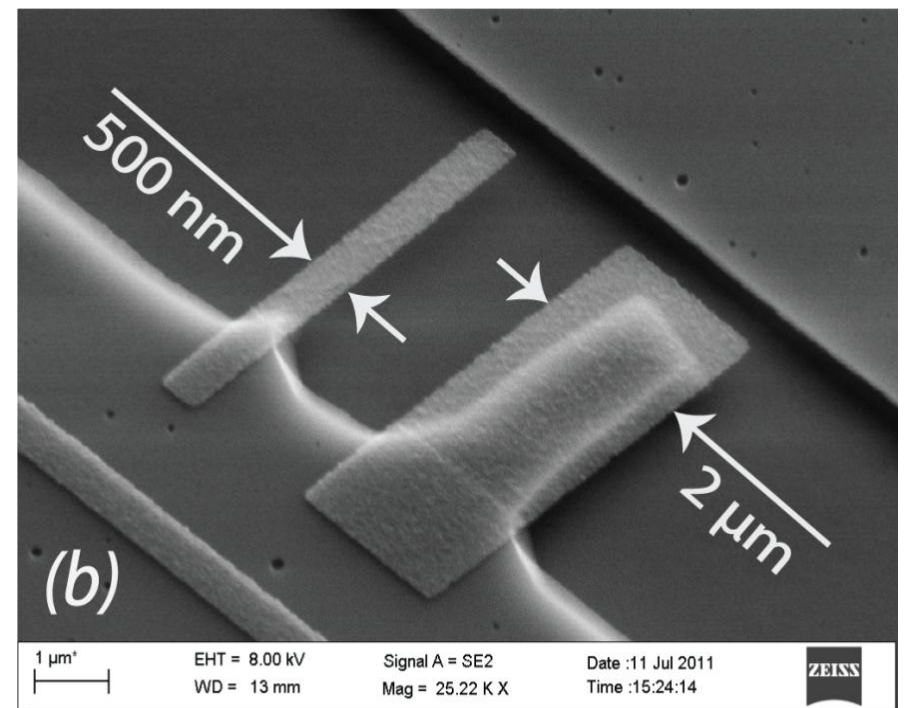
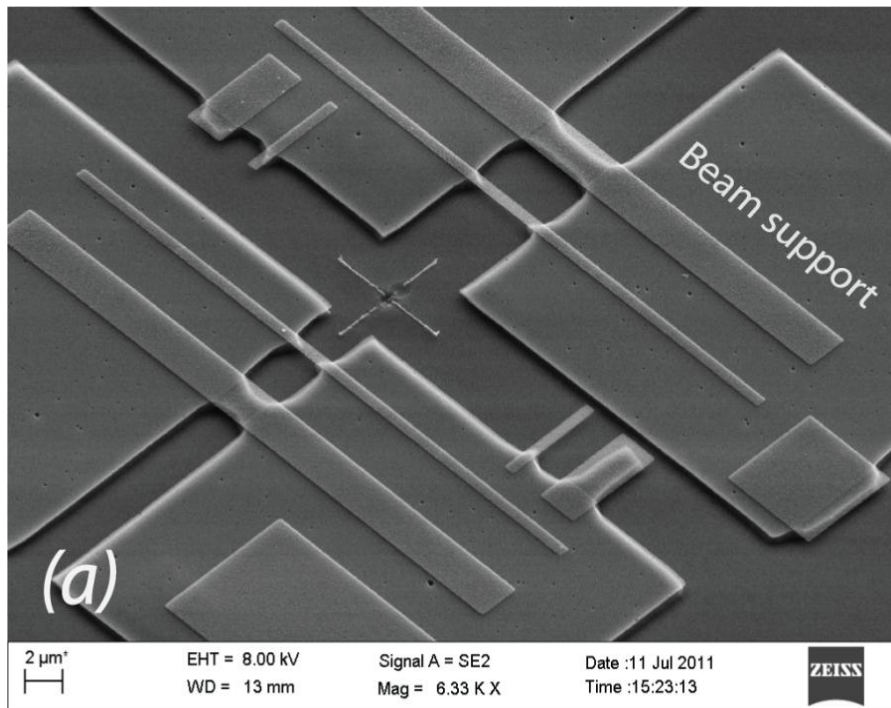




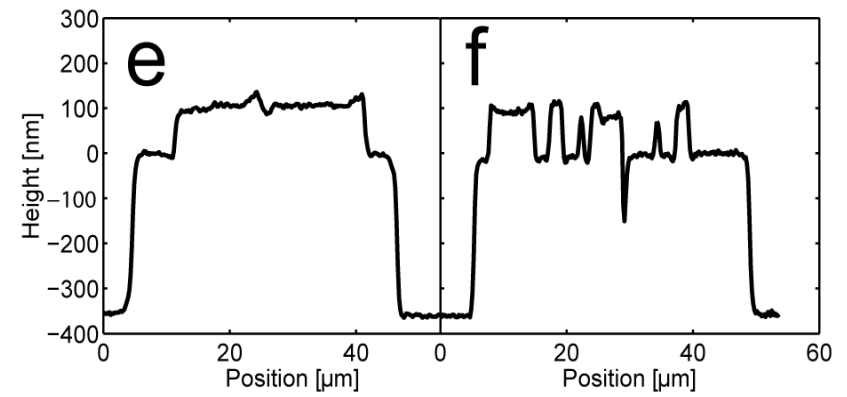
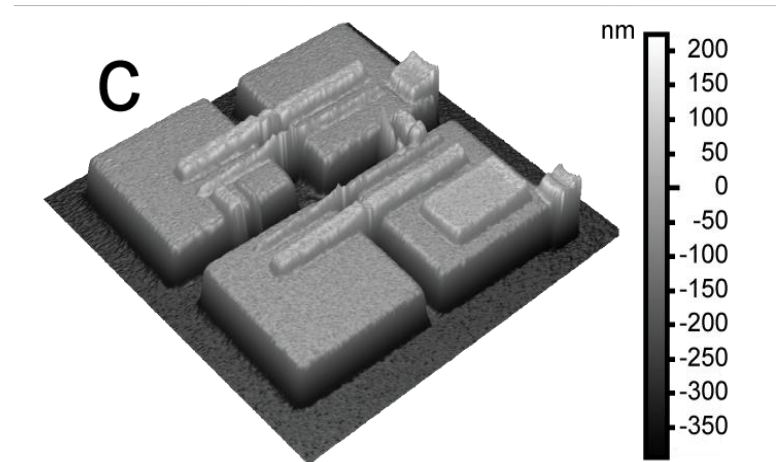
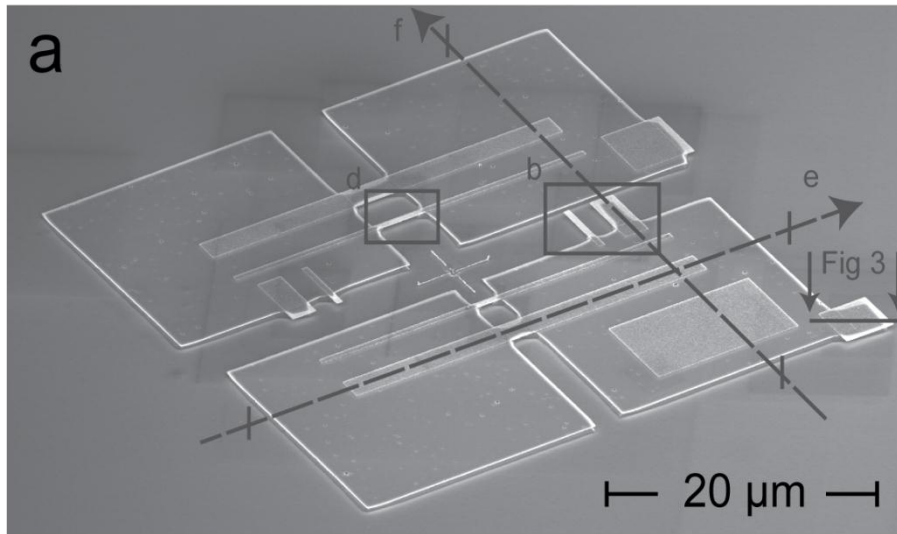
# 3D Printing Process for Si Nano Devices



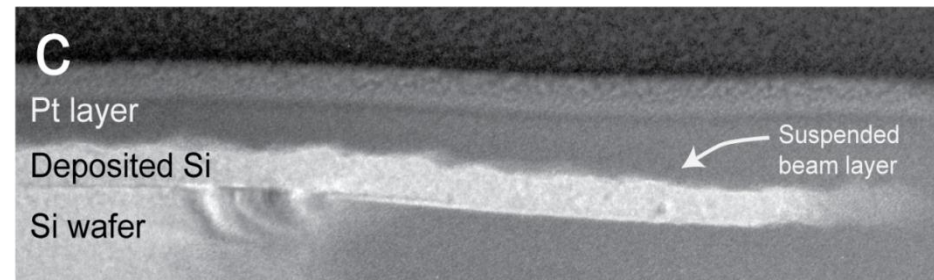
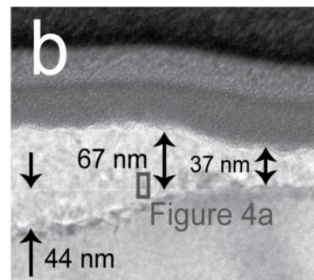
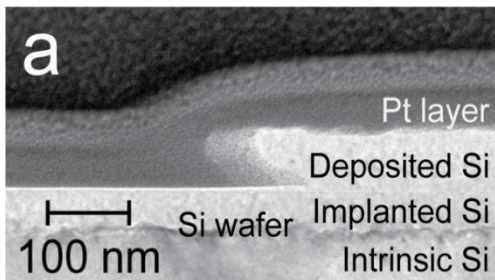
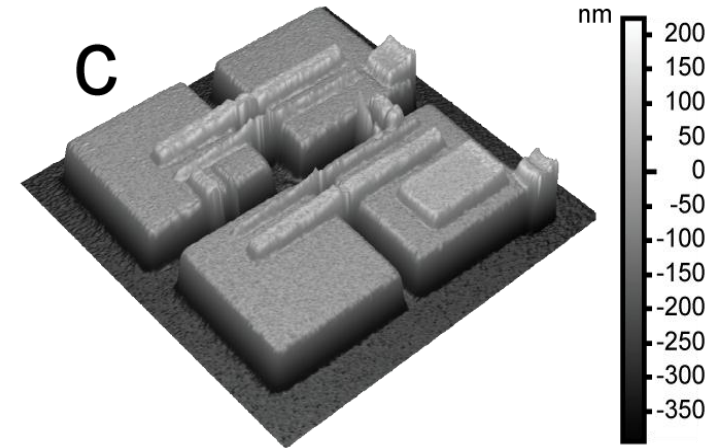
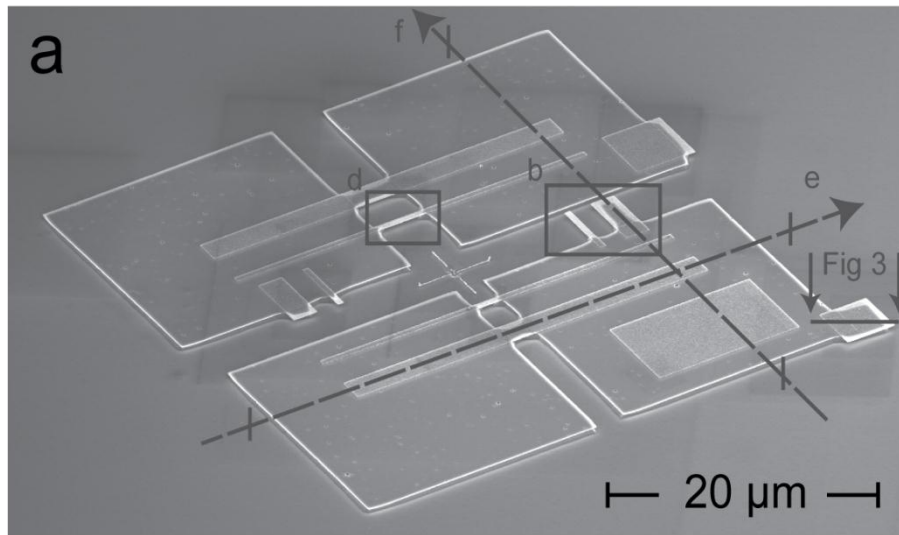
# 3D Printing of Si Micro and Nano Devices



# 3D Printing of Si Micro and Nano Devices

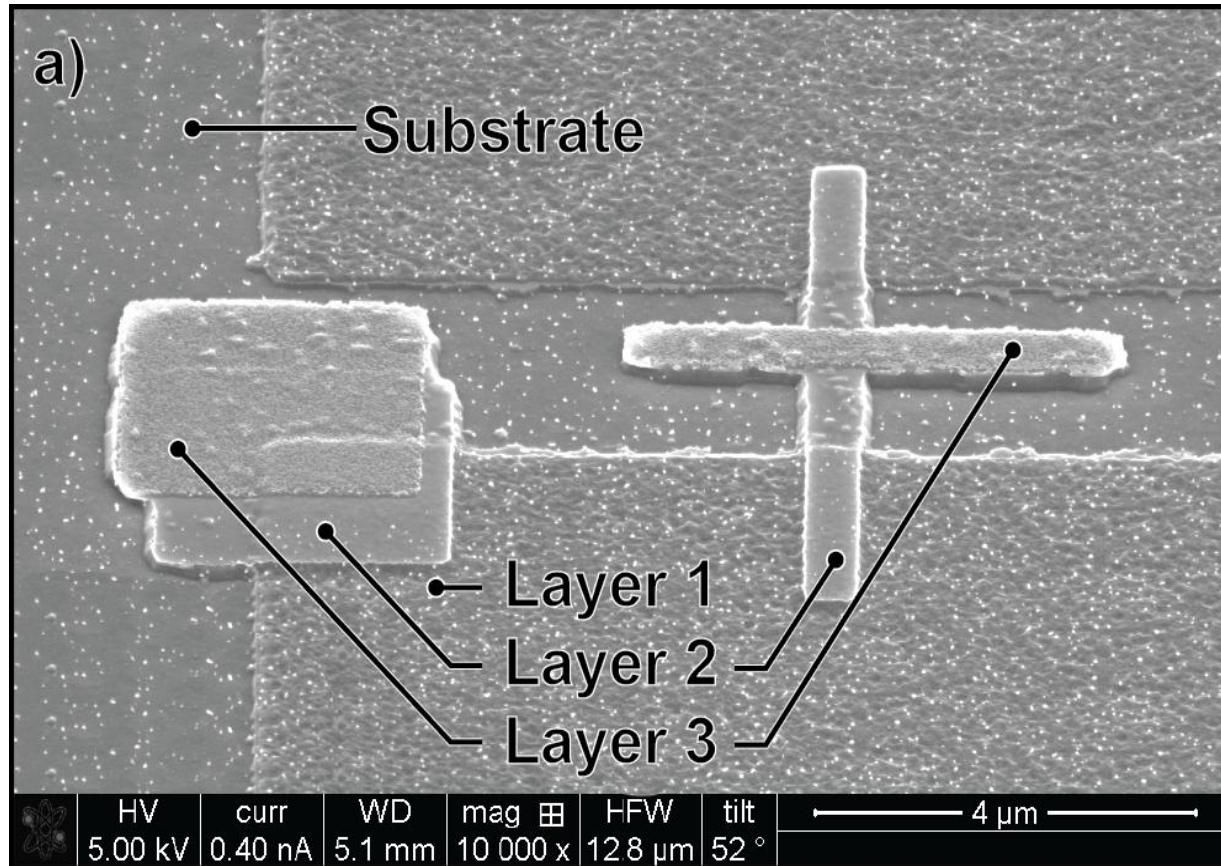


# Cross Section of Si Nano Devices



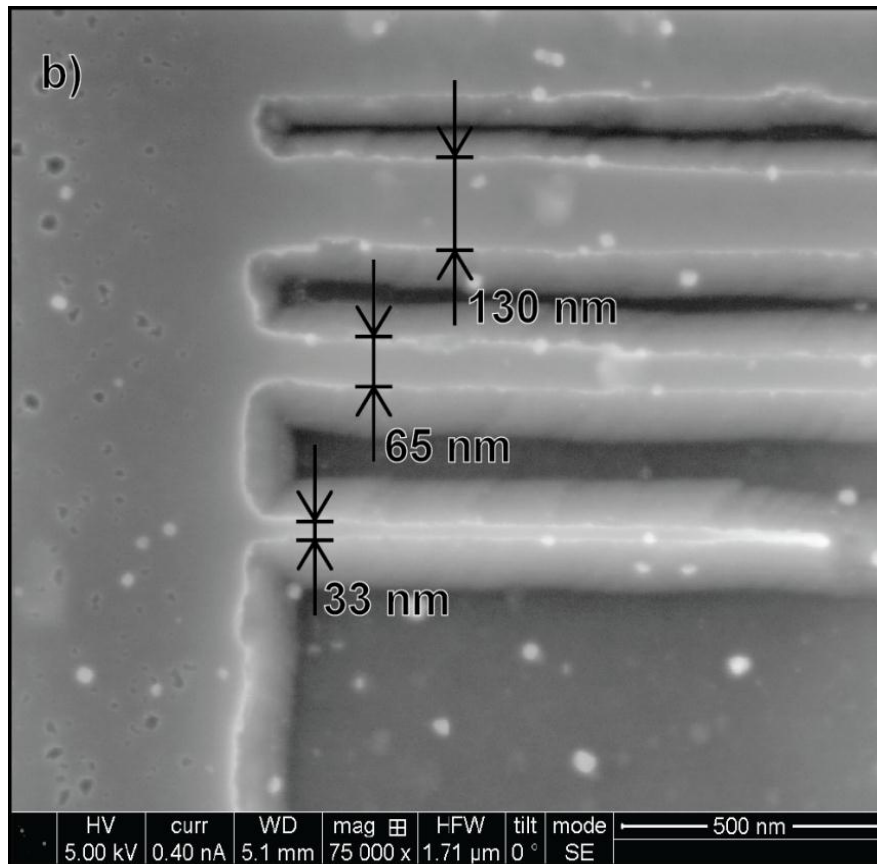


# 3-Layer 3D Printed Si Micro-Structures





# Resolution Limits of 3D Si Printed Nano-Structures



- Line-width resolution of 33 nm demonstrated.
- Line-width resolution of 20 nm with FIB writing, reported in literature.
- Layer thickness on the order of 35-70 nm.